

Principles of Micro- and Nanofabrication for Electronic and Photonic Devices

Introduction

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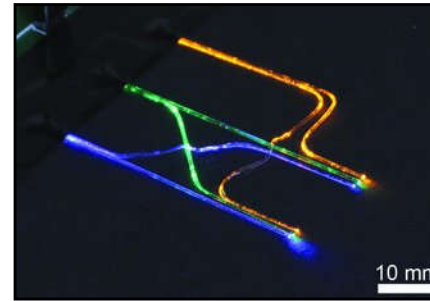
Optical and Electronic Devices



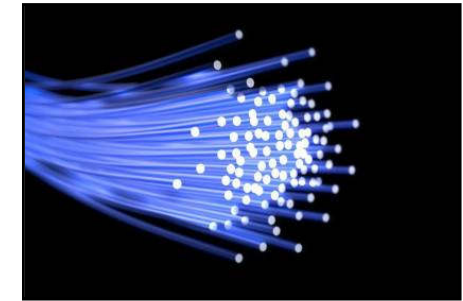
LEDs



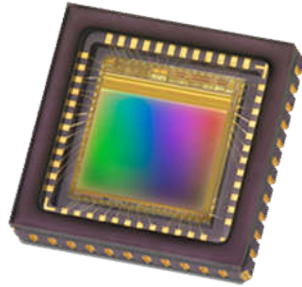
lasers



waveguides



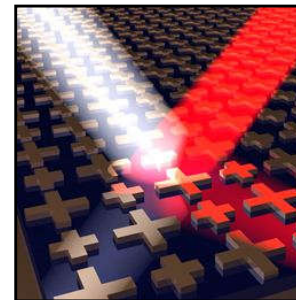
fibers



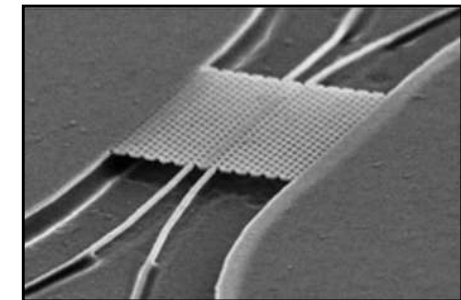
detectors



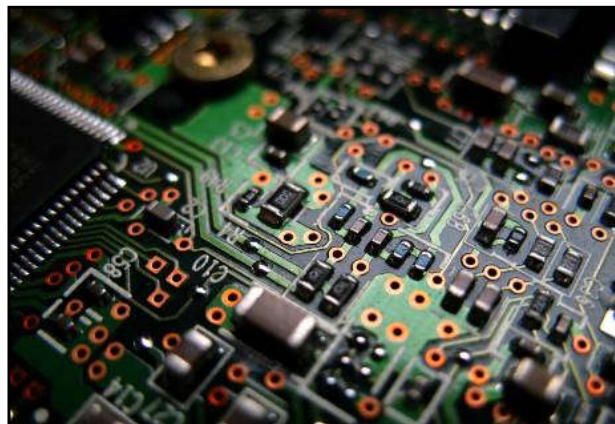
solar cells



metamaterials



photonic crystals



integrated circuits



Airflow Sensors



Current Sensors



Fiber Optics and Liquid Level Sensors



Flexible Heaters



Force Sensors



Humidity Sensors



Infrared Sensors



Magnetic Sensors



Proximity Sensors



Rotary Position Sensors



Speed Sensors

Goal of This Course

- Focus on the **fabrication and processing methods** to form electronic and optical devices at micro- and nano-scale
- Cover fundamental concepts to **grow, pattern, deposit, etch and integrate** various materials (silicon, III-V, etc) to form electronic and optical devices
- **Emerging fabrication technologies** such as nanofabrication and self-assembly will also be included

Nobel Prize in Physics

- **1956** **Semiconductor transistors**
- **1991** **Liquid crystals**
- **2000** **Integrated circuits**
- **2000** **Semiconductor heterostructures**
- **2009** **CCD imaging sensors**
- **2009** **Optical fibers**
- **2010** **Graphene**
- **2014** **GaN based blue LEDs**

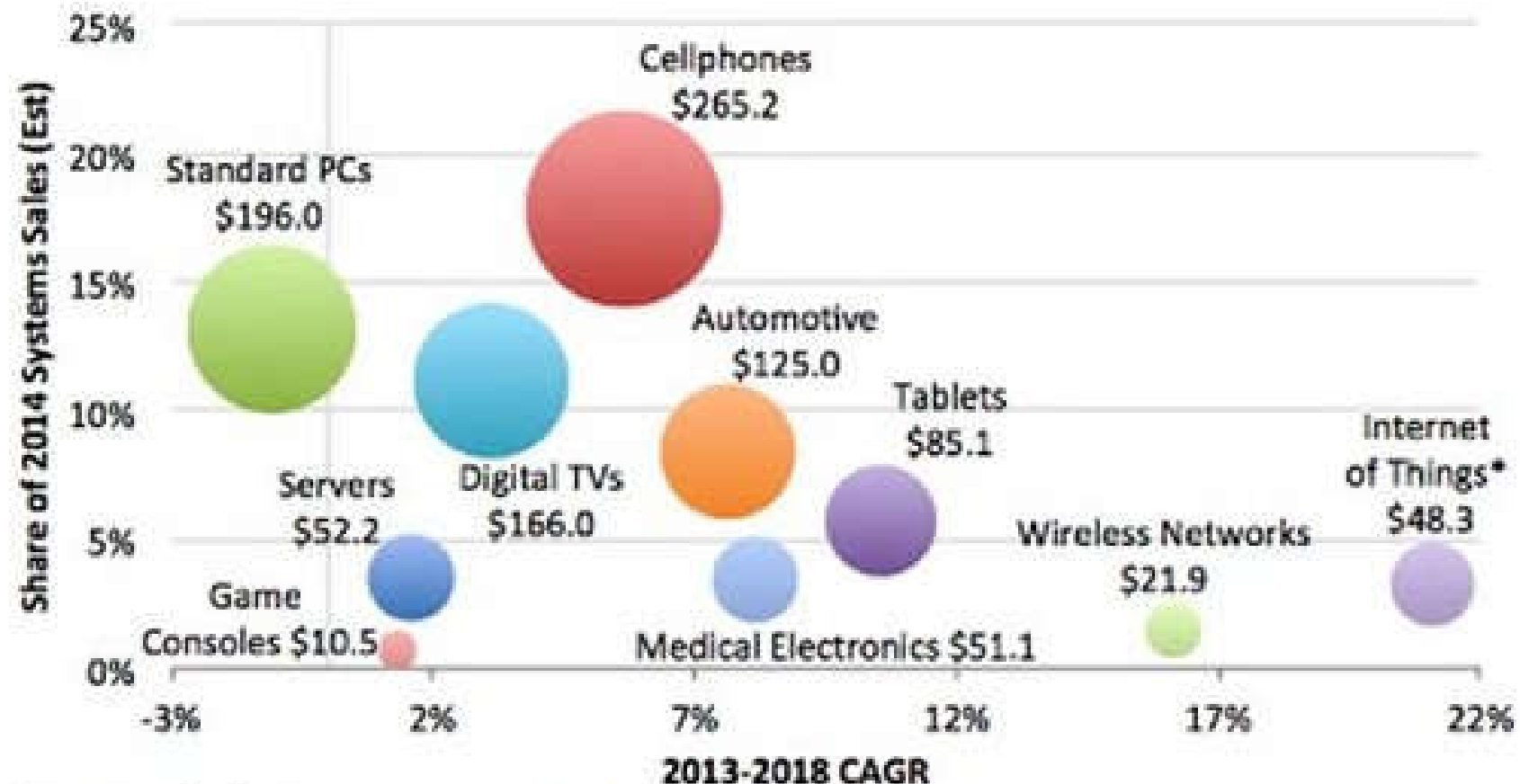
'Disruptive' Technologies

- 1956 Semiconductor transistors ← vacuum tubes
- 1991 Liquid crystals ← CRT displays
- 2000 Integrated circuits
- 2000 Semiconductor heterostructures
- 2009 CCD imaging sensors ← film cameras
- 2009 Optical fibers ← copper cables
- 2010 Graphene
- 2014 GaN based blue LEDs ← incandescent light bulbs

Semiconductor Market

current ~ 500 billion \$\$\$

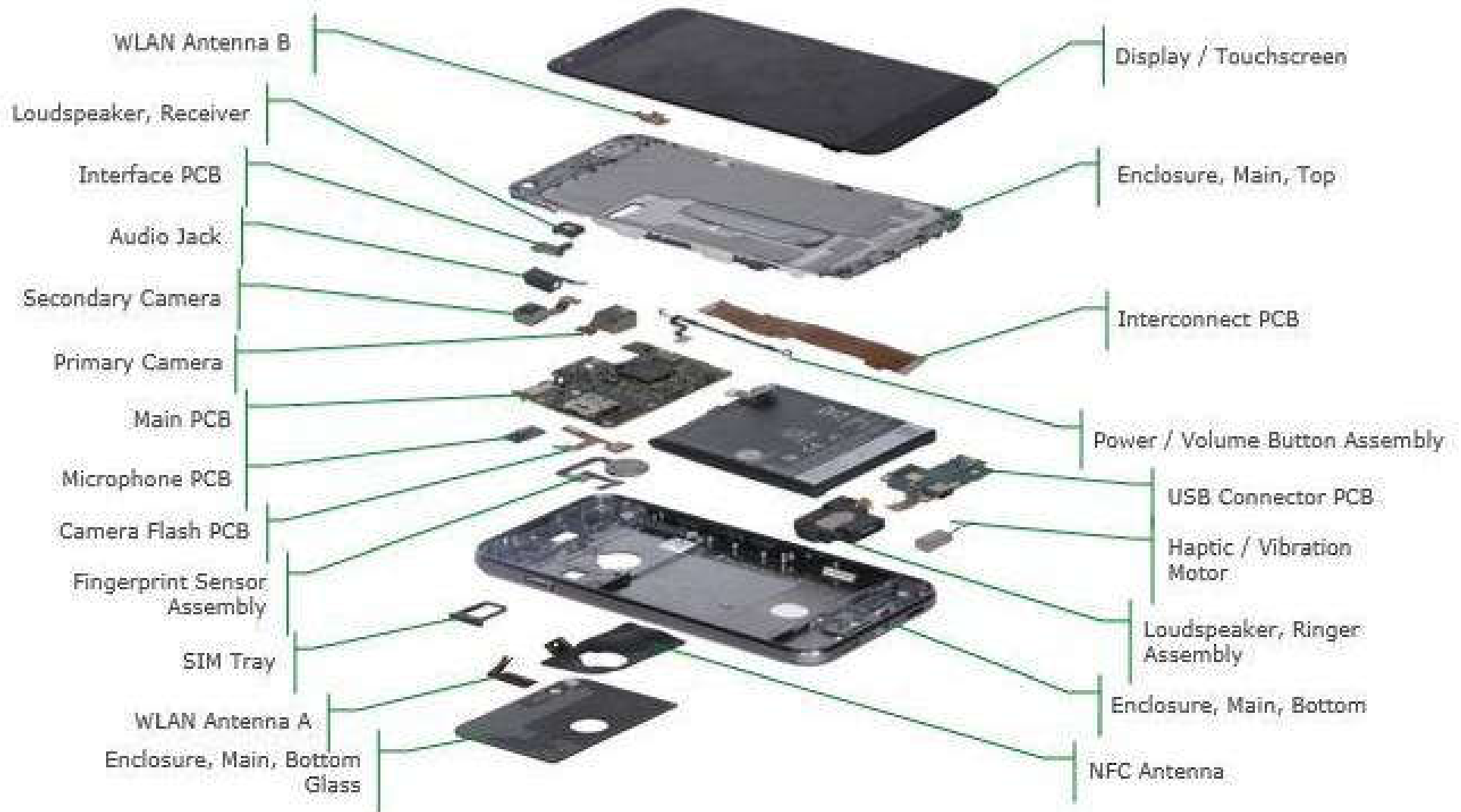
GDP of Thailand: 400 billion \$\$\$



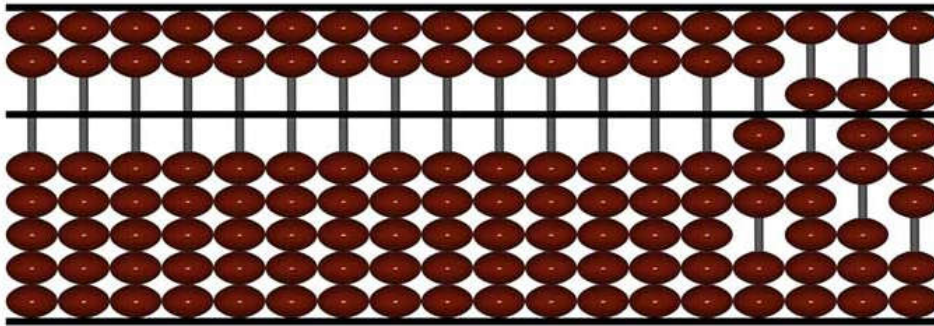
*Covers only the Internet connection portion of systems

Source: IC Insights

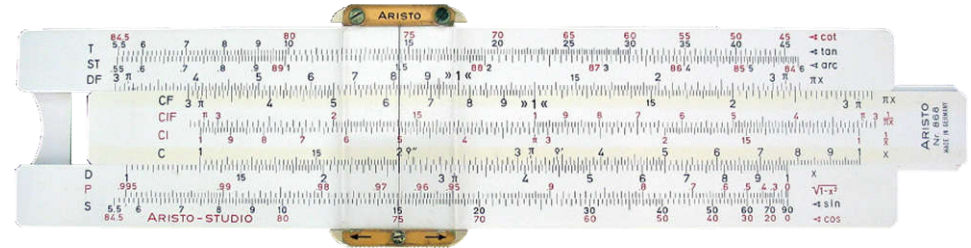
Devices in a Smartphone



Some 'Ancient' Computers



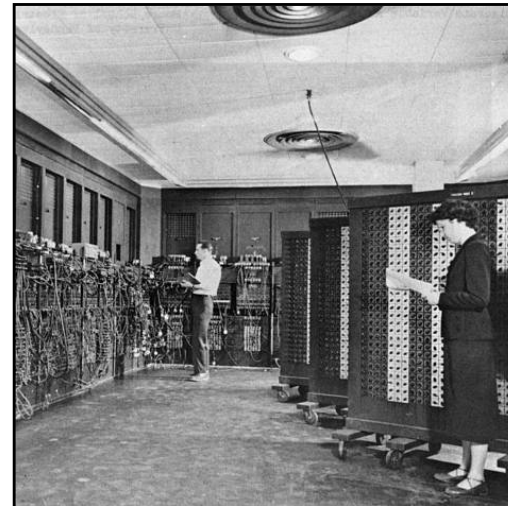
abacus



slide rule

■ First 'electronic' computer

- ❑ ENIAC, 1943
- ❑ 30 tons, 200 kW
- ❑ 18000 vacuum tubes
- ❑ 5000 times/sec
- ❑ cost \$480,000

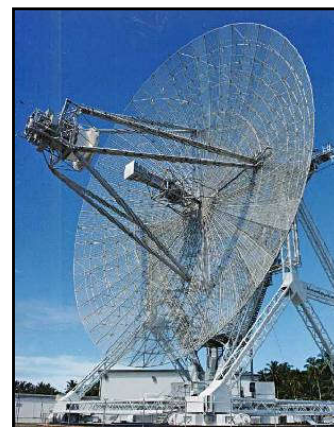
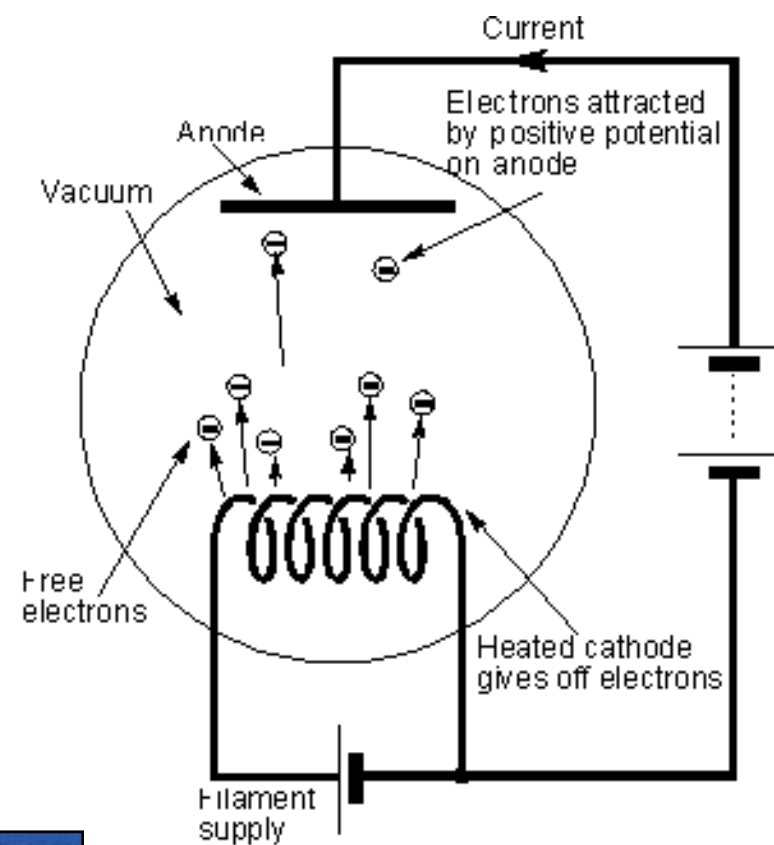


vacuum tube

Vacuum Tube



current flows only in one direction: *diode*



First Semiconductor Transistor

Germanium
Bipolar Transistor

The first point contact transistor
William Shockley, John Bardeen, and Walter Brattain
Bell Laboratories, Murray Hill, New Jersey (1947)

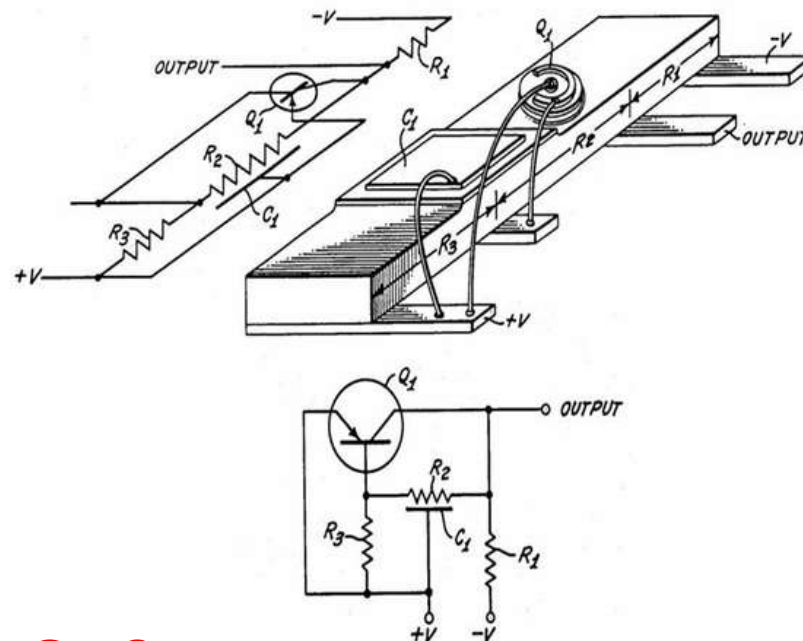


1956 Nobel Prize in Physics

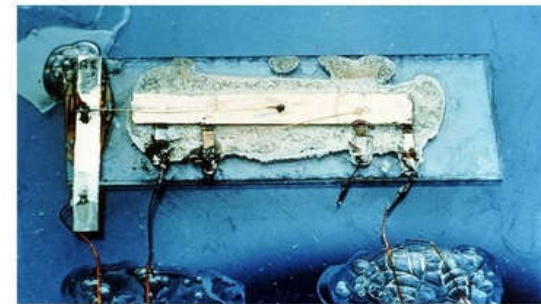
First Integrate Circuits

The First (2D) Integrated Circuit Jack Kilby, Texas Instruments, 1958

- Transistor, Resistors and Capacitors on the same piece of semiconductor
- **Interconnects between components not integrated**
→ Low connectivity between components



Germanium



J. Kilby
1923–2005

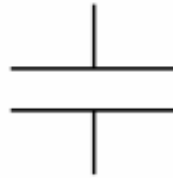
Q: Why Ge?

2000 Nobel Prize in Physics

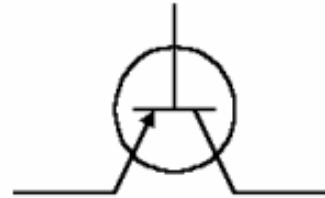
First Integrate Circuits



diode



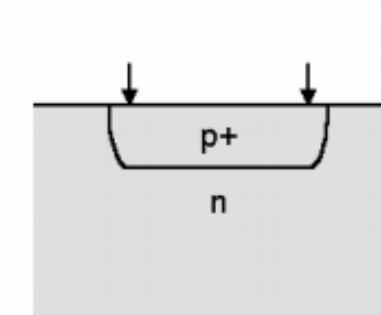
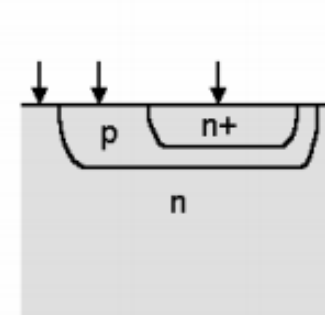
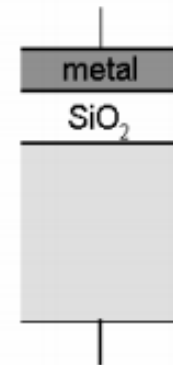
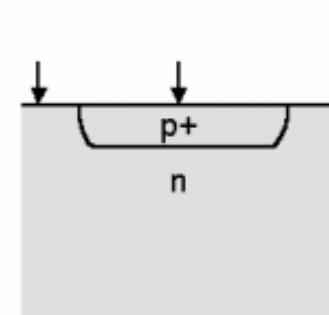
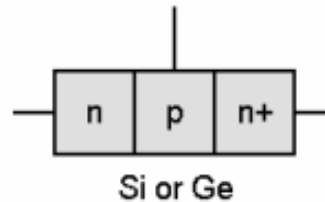
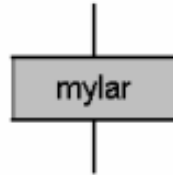
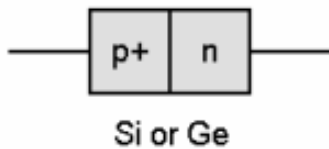
capacitor



transistor



resistor



All devices can be made in the same semiconductor!

First Integrate Circuits

"There is plenty of room at the bottom", APS Meeting, 1959

MINIATURIZING THE COMPUTER

I don't know how to do this on a small scale in a practical way, but I do know that computing machines are very large; they fill rooms. Why can't we make them very small, make them of little wires, little elements—and by little, I mean *little*. For instance, the wires should be 10 or 100 atoms in diameter, and the circuits should be a few thousand angstroms across. Everybody who has analyzed the logical theory of computers has come to the conclusion that the possibilities of computers are very interesting—if they could be made to be more complicated by



R. Feynman

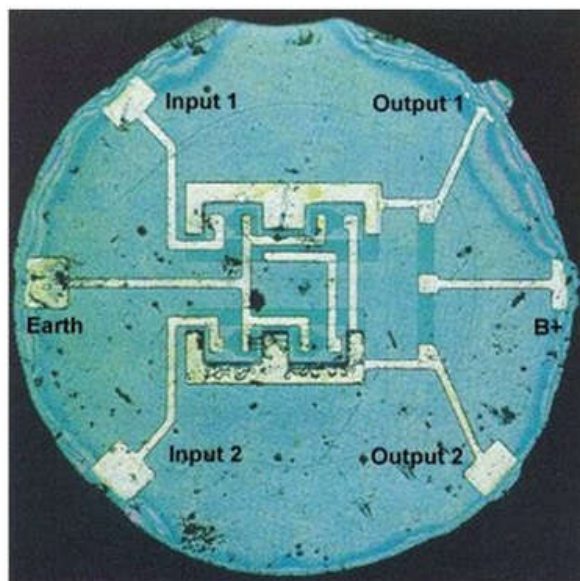
First Integrate Circuits

The First *Monolithic* (2D) Integrated Circuit Robert Noyce, Fairchild Semiconductor, 1961

- Transistor, Resistors and Capacitors on the same piece of semiconductor
- **Interconnects between components integrated**
→ High connectivity between components

Silicon

4 transistors



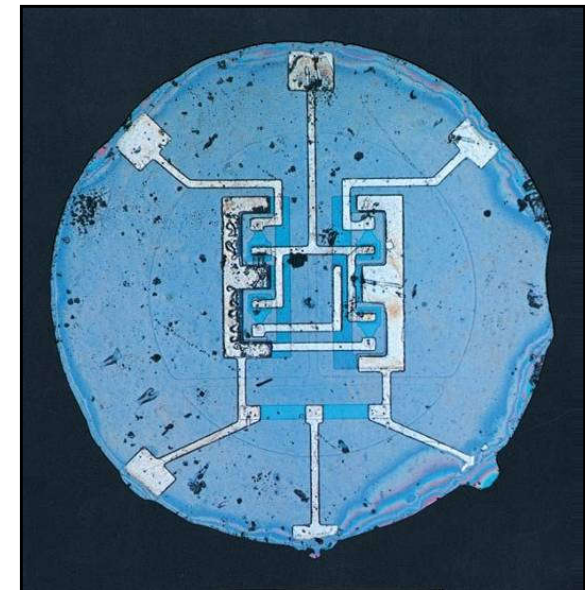
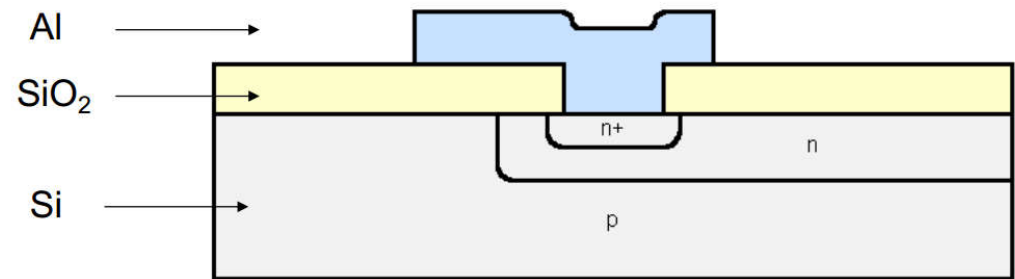
~ 2 mm



R. Noyce
1927–1990

First Integrate Circuits

- Thermal oxidation (SiO_2)
- Photolithography
- Etching
- Thermal diffusion (n-Si, p-Si)
- Metal deposition (Al)

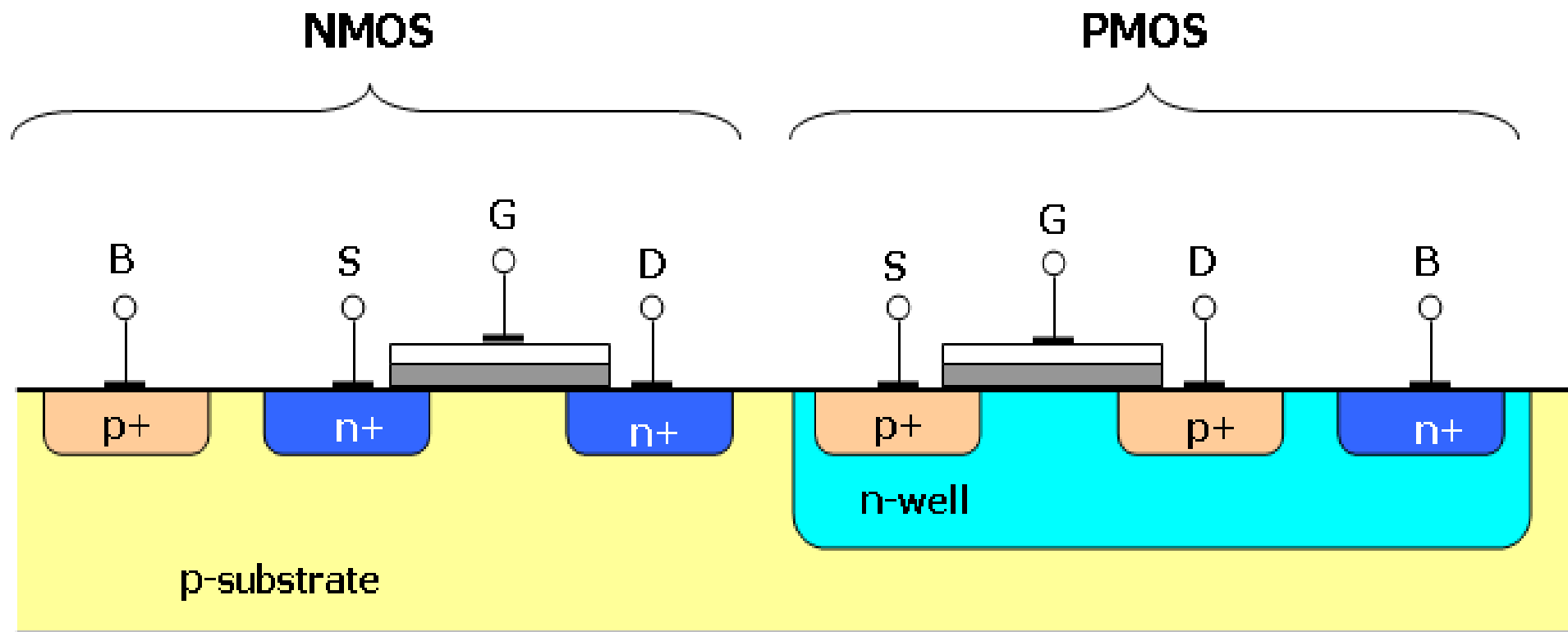


~ 2 mm

Very similar to today's process

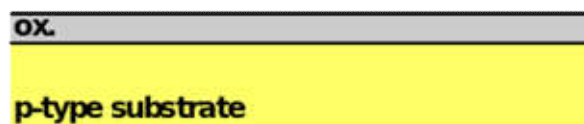
CMOS

- **Complementary Metal-Oxide-Semiconductor**
 - **F. Wanlass, Fairchild, 1963**

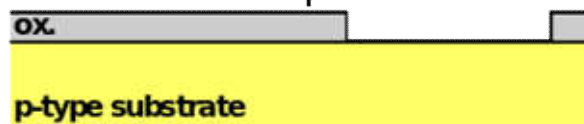


CMOS Process

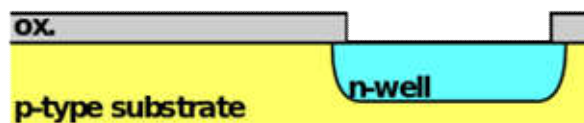
1. Grow field oxide



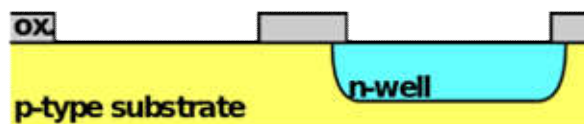
2. Etch oxide for pMOSFET



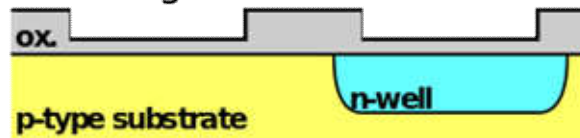
3. Diffuse n-well



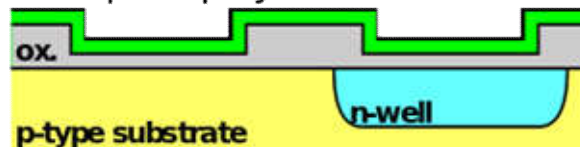
4. Etch oxide for nMOSFET



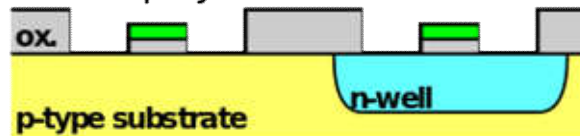
5. Grow gate oxide



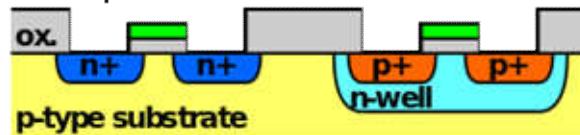
6. Deposit polysilicon



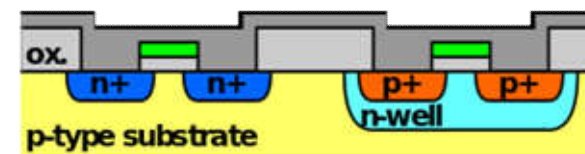
7. Etch polysilicon and oxide



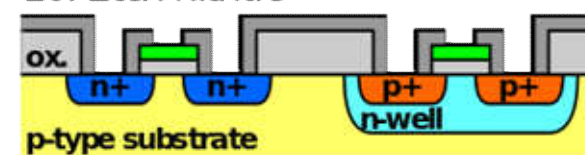
8. Implant sources and drains



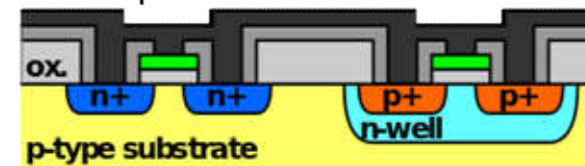
9. Grow nitride



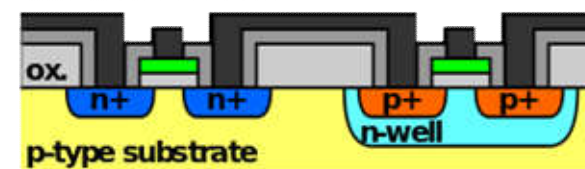
10. Etch nitride



11. Deposit metal

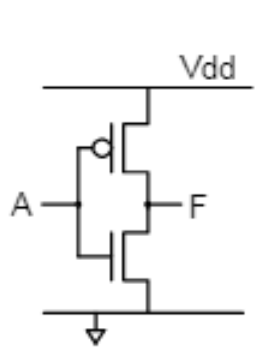


12. Etch metal



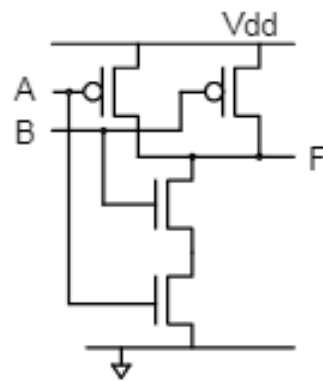
[Video](#)

CMOS Logic



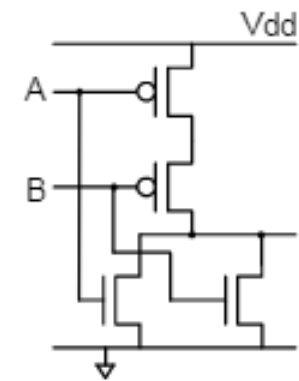
A	F
L	H
H	L

CMOS INVERTER



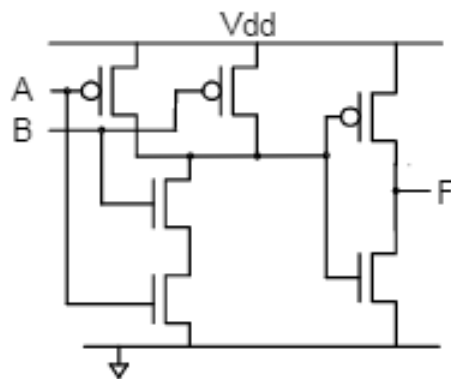
A	B	F
L	L	H
L	H	H
H	L	H
H	H	L

CMOS NAND



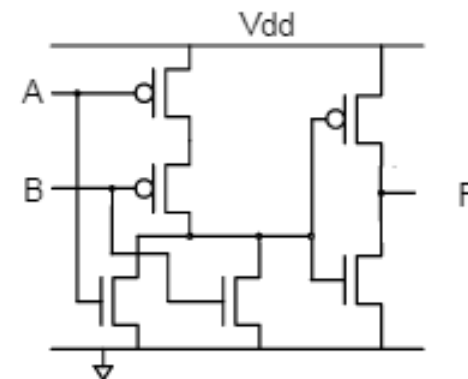
A	B	F
L	L	H
L	H	L
H	L	L
H	H	L

CMOS NOR



A	B	F
L	L	L
L	H	L
H	L	L
H	H	H

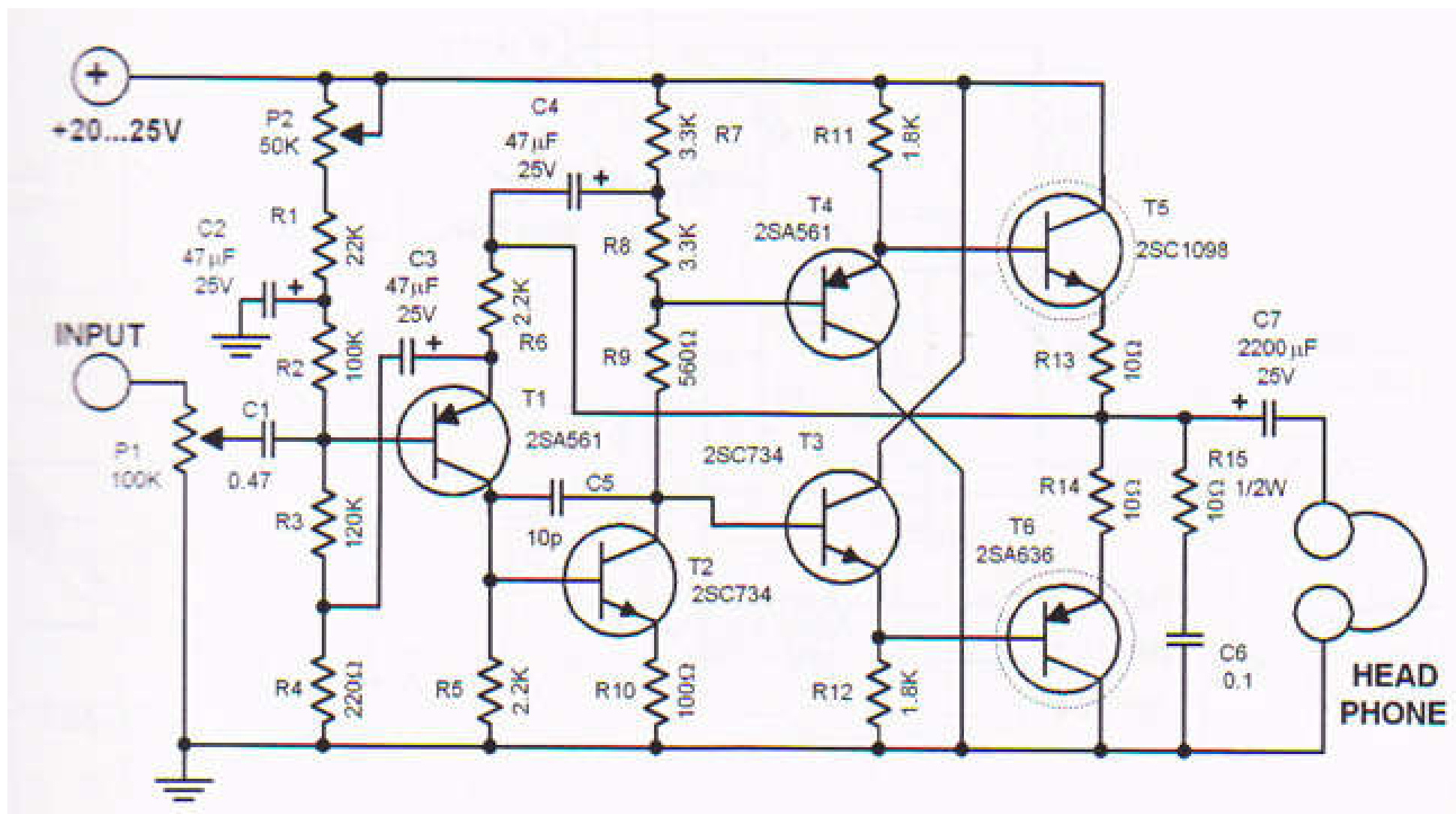
CMOS AND



A	B	F
L	L	L
L	H	H
H	L	H
H	H	H

CMOS OR

CMOS Circuit

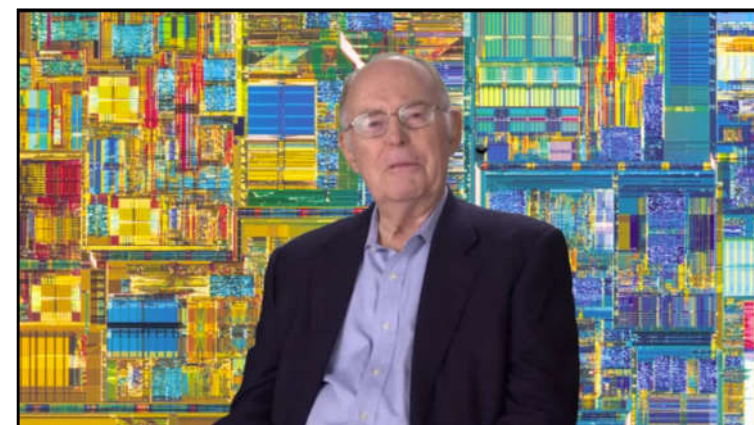


Integrate Circuits

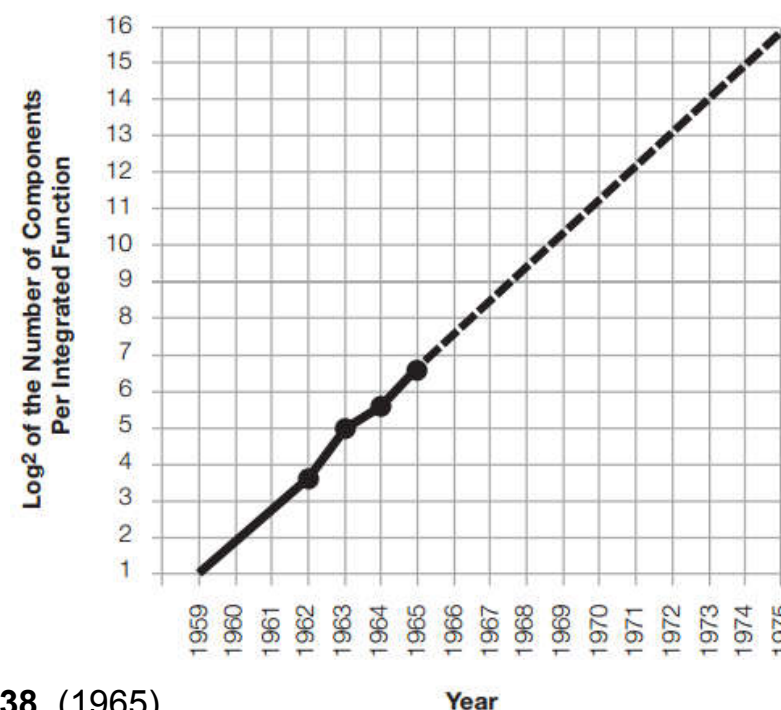
■ Moore's law, Fairchild, 1965

The complexity for minimum component costs has increased at a rate of roughly a factor of two per year (see graph on next page). Certainly over the short term this rate can be expected to continue, if not to increase. Over the longer term, the rate of increase is a bit more uncertain, although there is no reason to believe it will not remain nearly constant for at least 10 years. That means by 1975, the number of components per integrated circuit for minimum cost will be 65,000.

I believe that such a large circuit can be built on a single wafer.

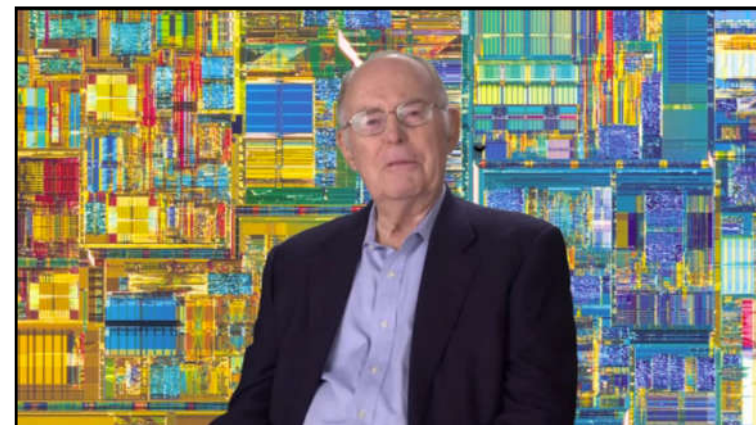


G. Moore



Integrate Circuits

- Moore's law, Fairchild, 1965

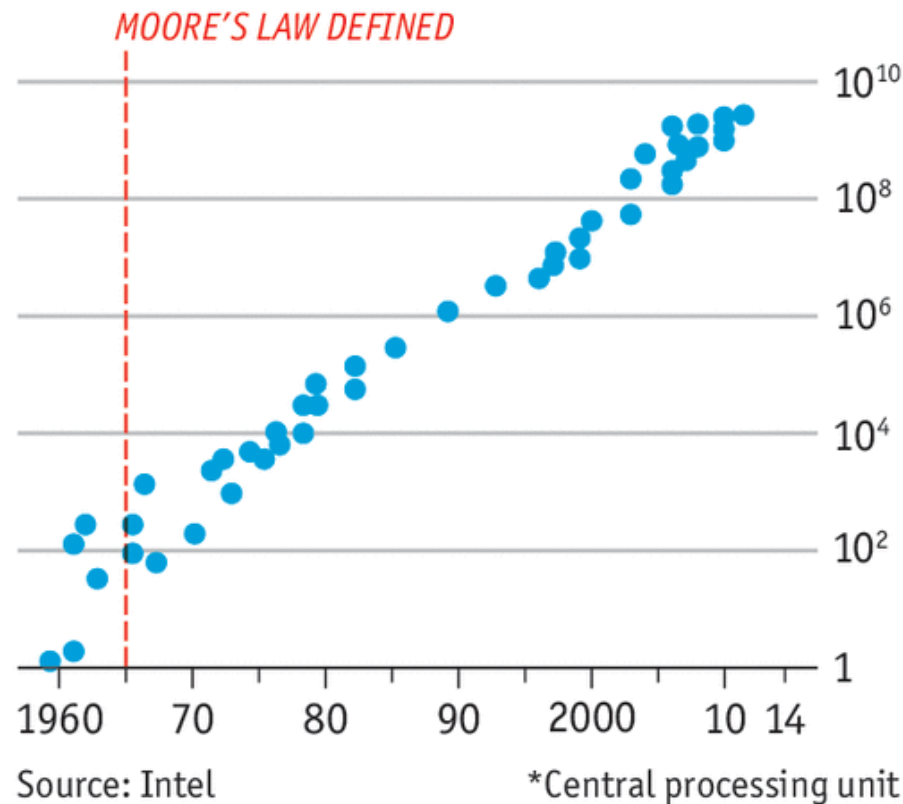


G. Moore



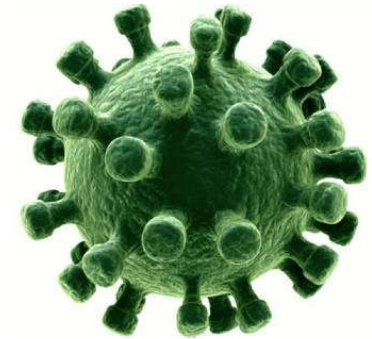
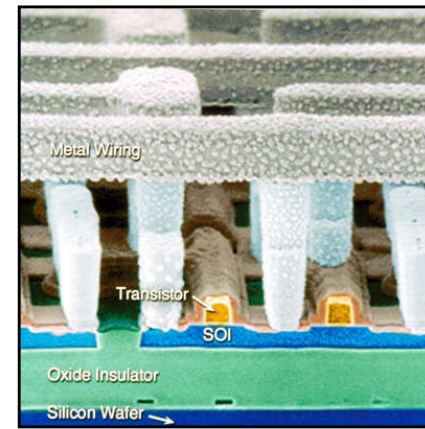
Integrate Circuits

- Moore's law, Fairchild, 1965



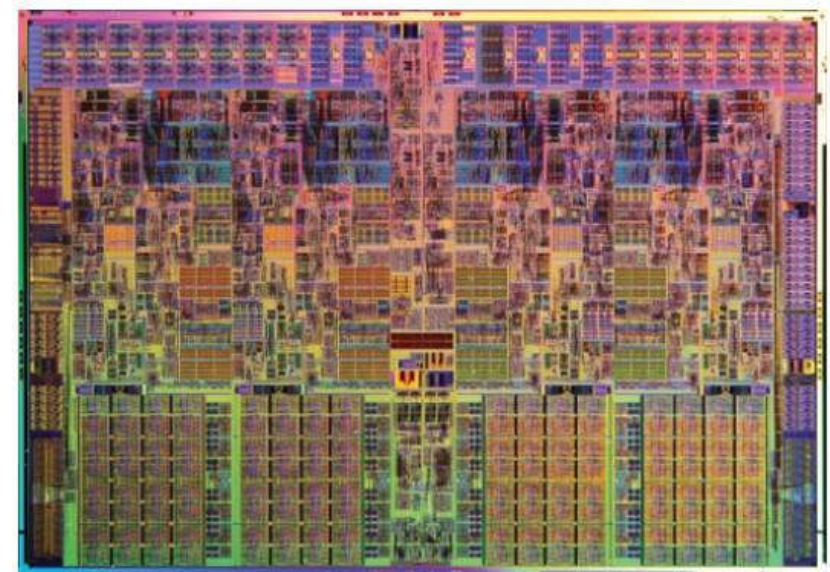
Economist.com

Modern Electronics is a real Nanotechnology



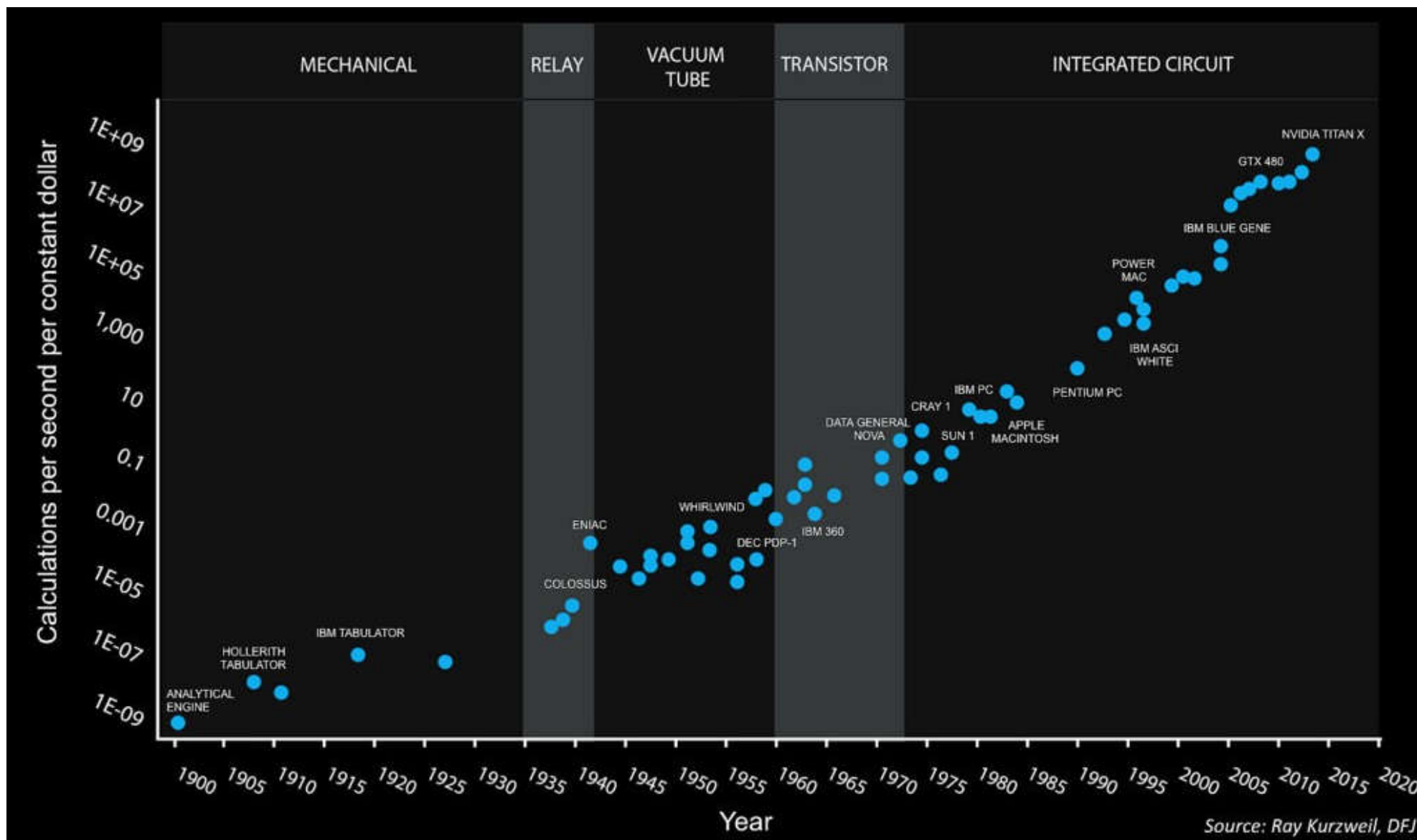
virus

< 100 nm



Intel i7 CPU, ~ 10⁹ transistors

120 Years of Moore's Law



Integrate Circuits

**the 10-Megabyte
Computer System**



**Only
\$5995
COMPLETE**

New From IMSAI

- 10-Megabyte Hard Disk
- 5 1/4" Dual-Density Floppy Disk Back-up
- 8-Bit Microprocessor (Optional 16-bit Microprocessor)
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*You Read It Right —
All for \$5995!*

IMSAI ... Thinking ahead for the 80's

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1980s



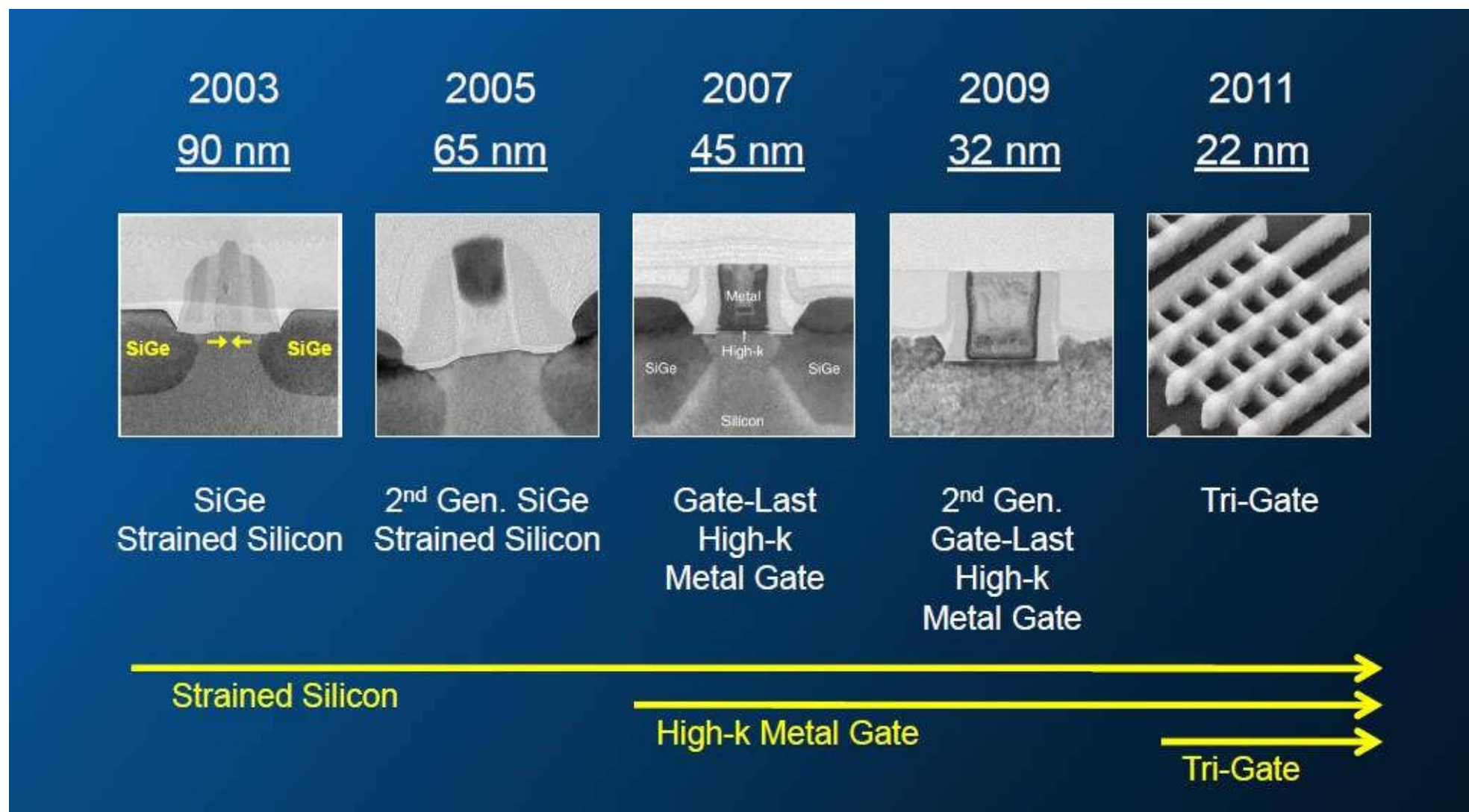
¥2549.00

英特尔 (Intel) 酷睿四核I7-7700k 盒装

CPU处理器 采用KabyLake架构, LGA 1151

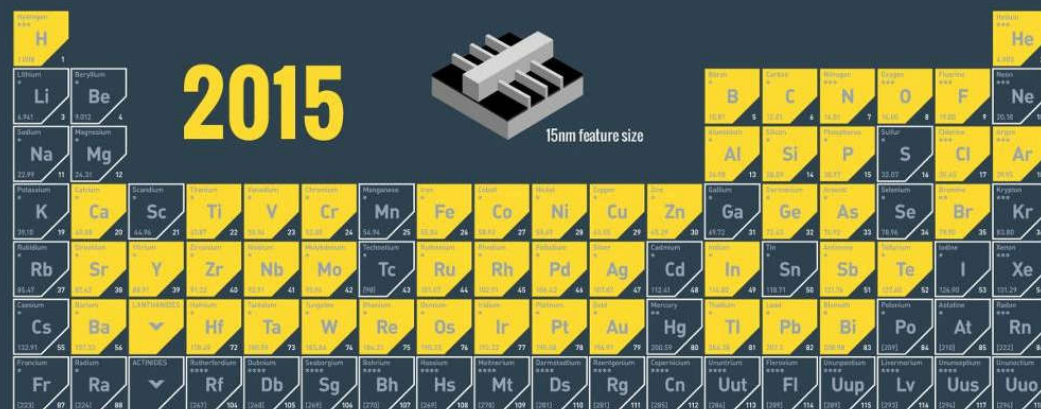
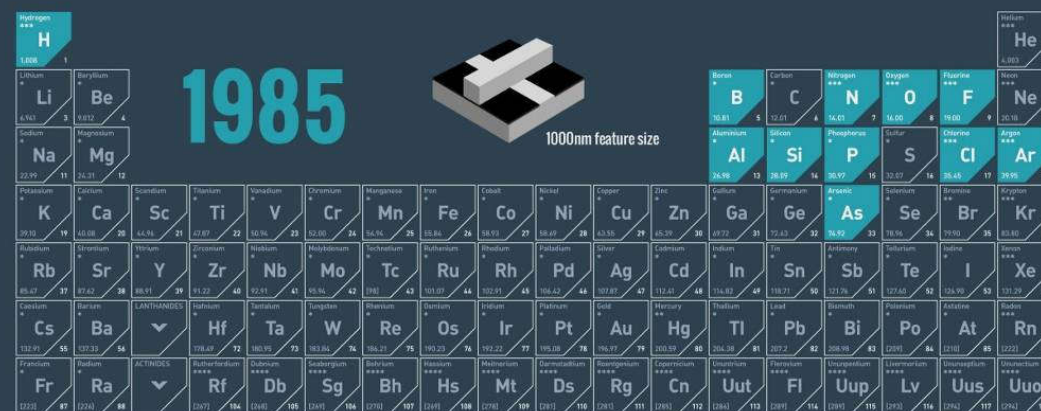
2017, price > gold

Transistor Evolution



Materials in IC

In the 1980s, the typical semiconductor used only a fraction of the primary elements.
Today, six times as many elements are used - more than half of the periodic table.



Source: Intel, SanDisk, Intermolecular

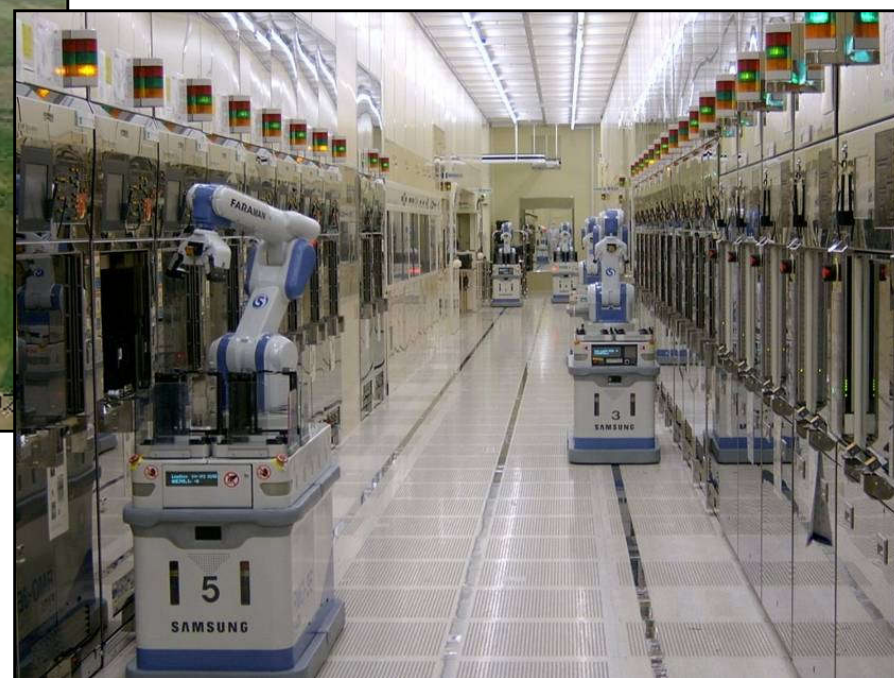
Modern IC foundry

Video 1

Video 2 Intel



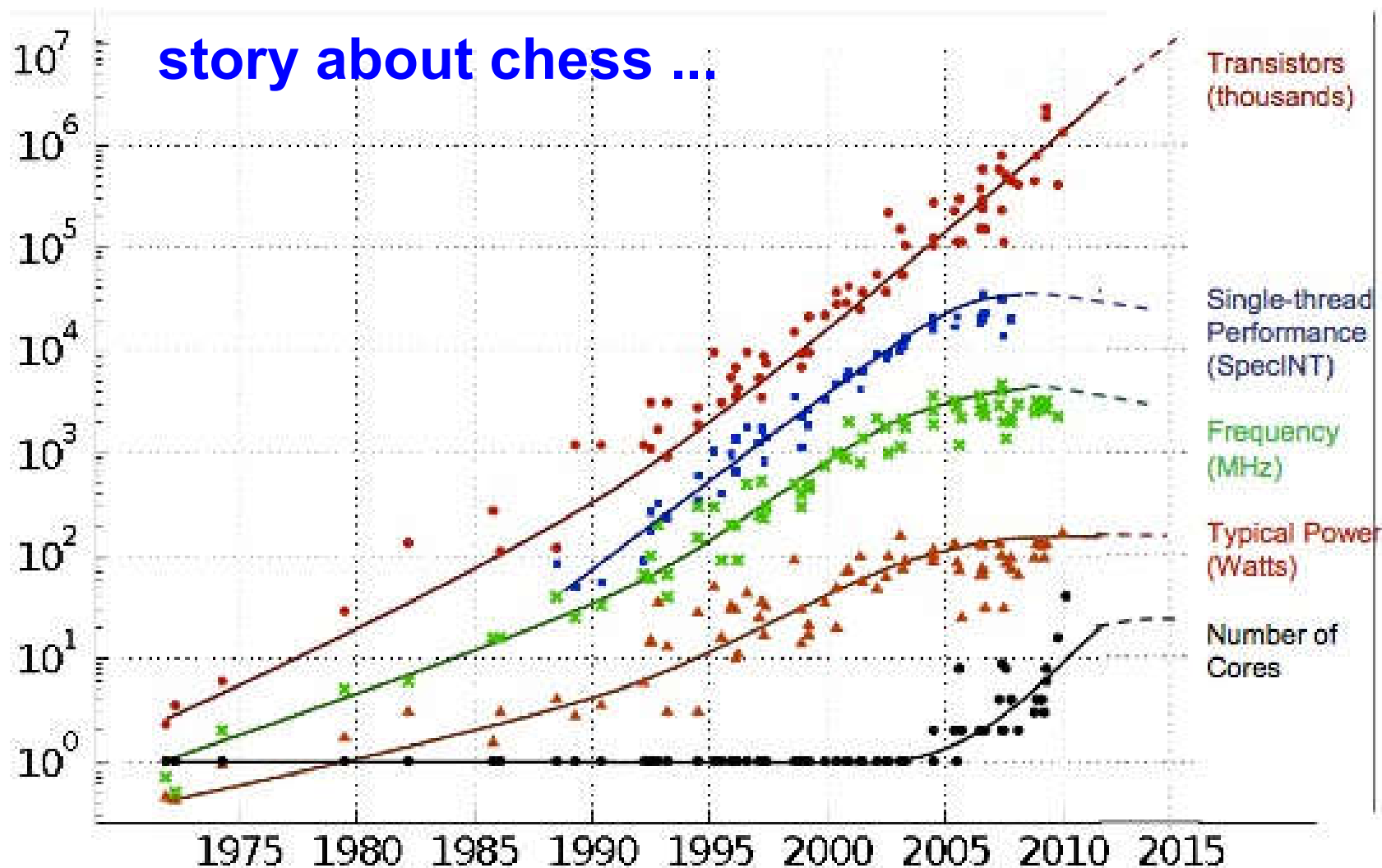
Global Foundries



Samsung

Cost > 10 billion \$\$\$

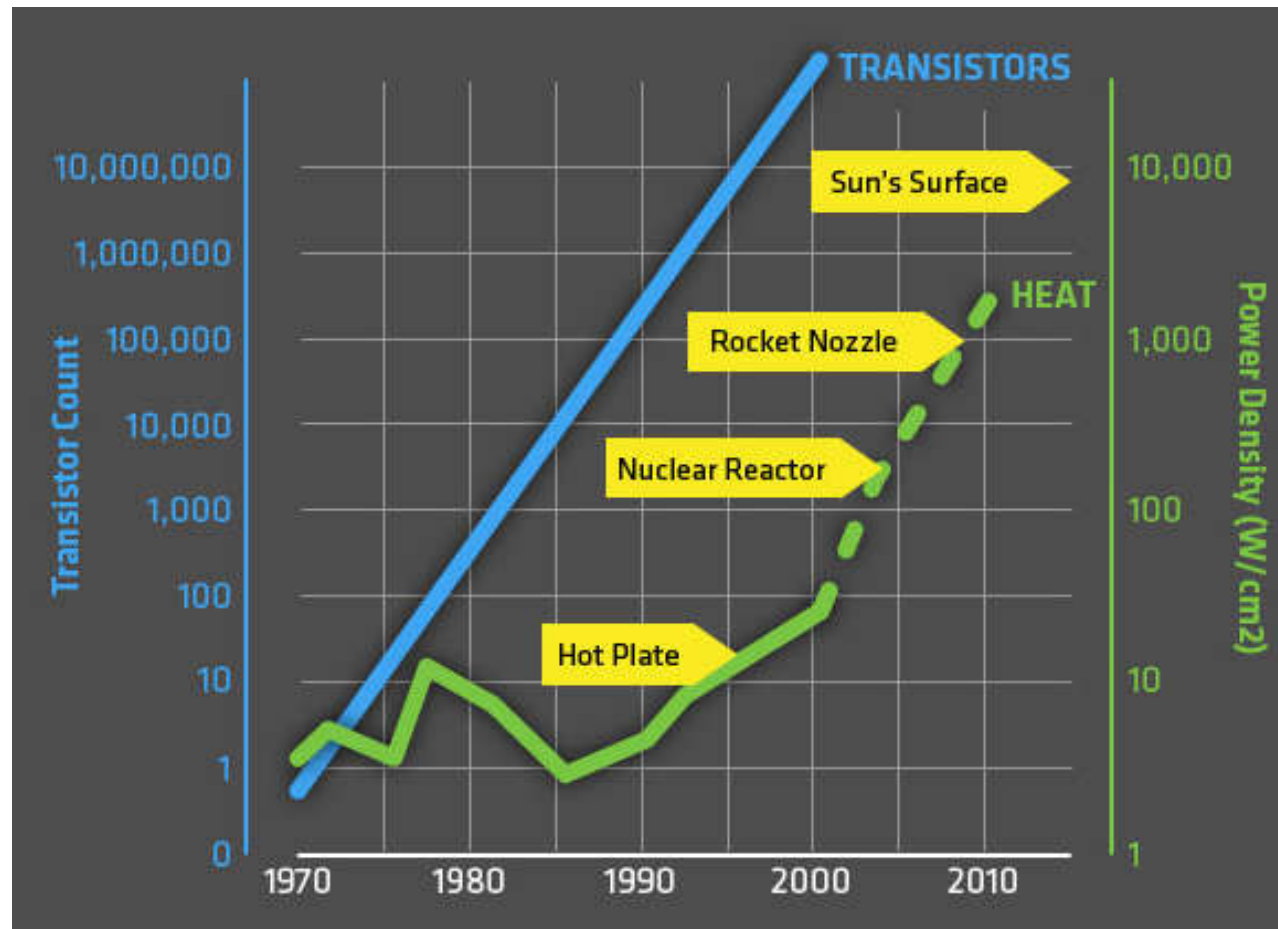
All Good Things Come to an End



Original data collected and plotted by M. Horowitz, F. Labonte, O. Shacham, K. Olukotun, L. Hammond and C. Batten
Dotted line extrapolations by C. Moore

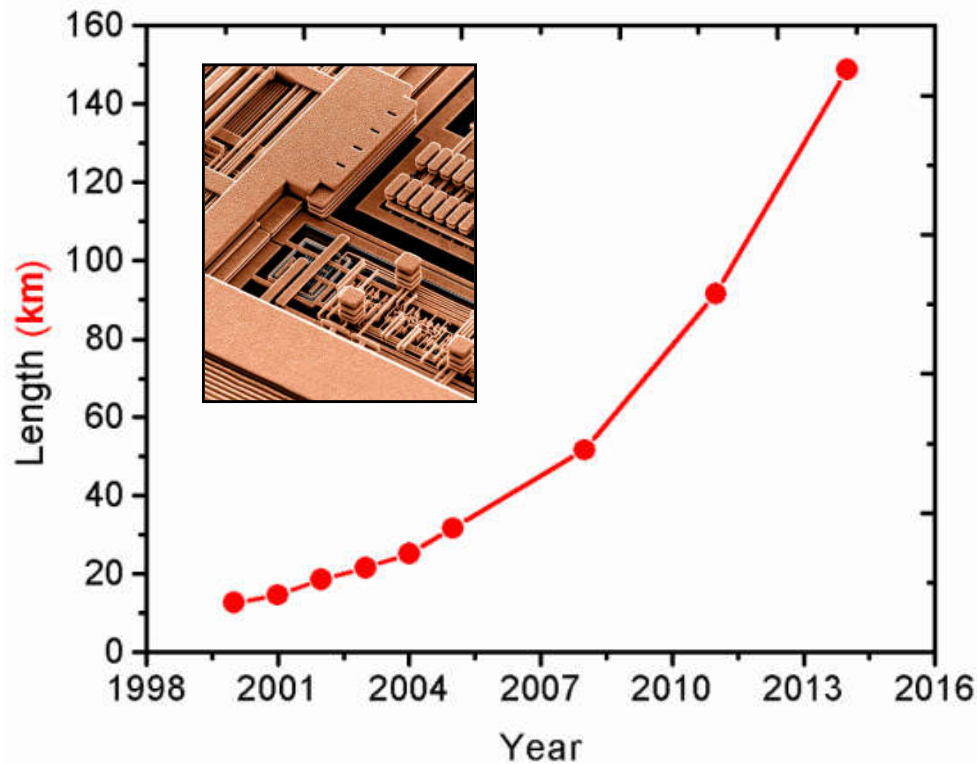
Power Consumptions

Shannon-von Neumann-Landauer (SNL) limit:
minimum energy per bit $\sim k_B T \cdot \ln(2)$



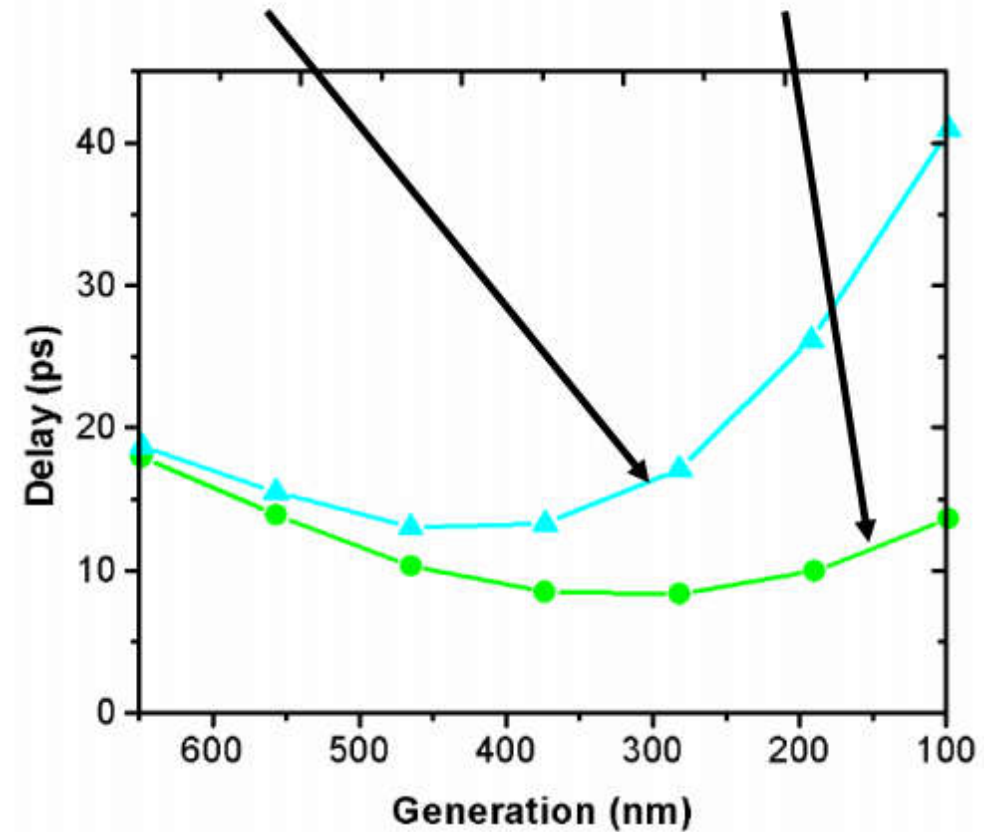
IC Delays

$$t \sim RC$$



total delay
for Al/SiO₂

total delay
for Cu/low-k

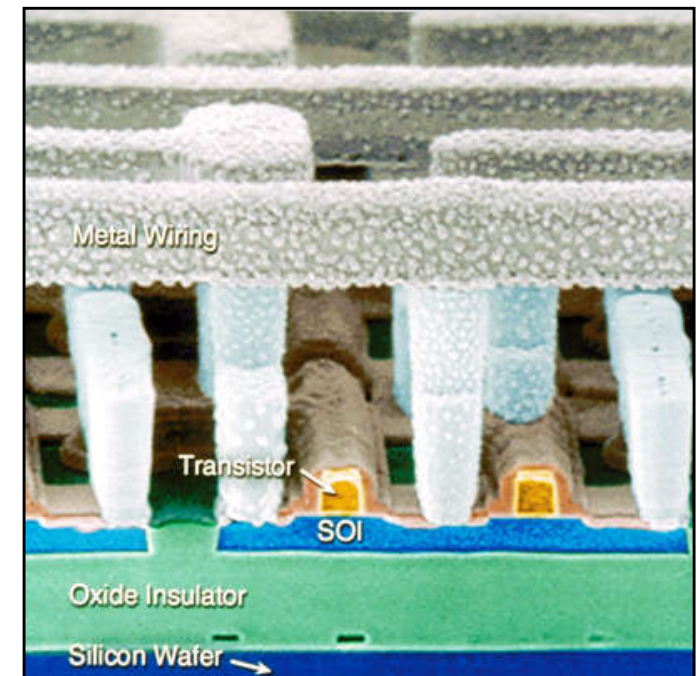


more conductive electrodes, lower k dielectrics

Doping in Nano Devices

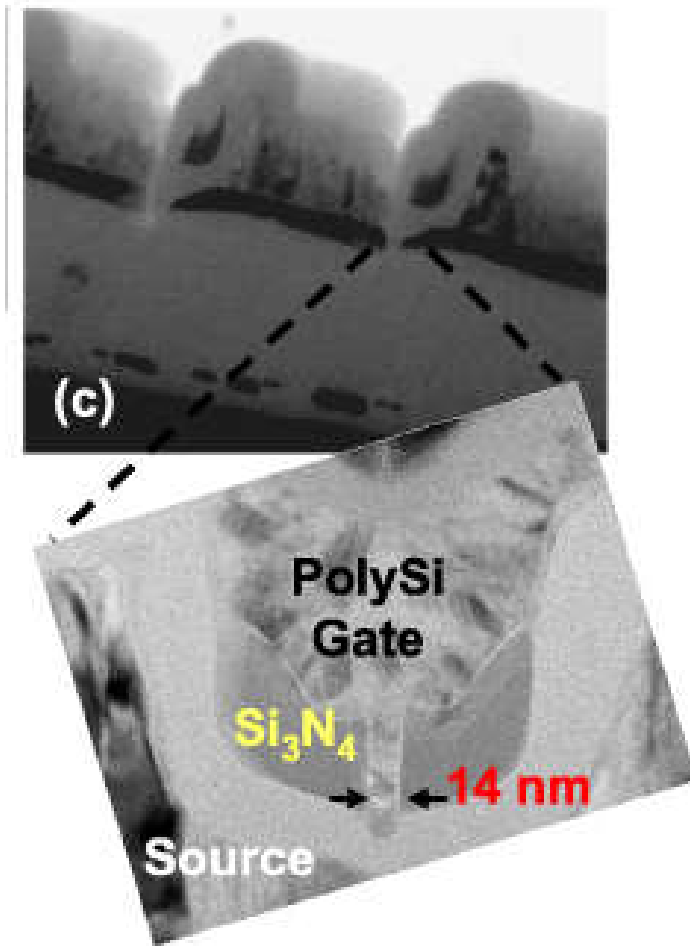
*atomic density of Si = $5 * 10^{22} / \text{cm}^3$*

if the transistor size is
 $10 \text{ nm} * 10 \text{ nm} * 10 \text{ nm}$,
and doping concentration is
 $1 * 10^{18} / \text{cm}^3$



There is only 1 dopant atom in the transistor!

Grain Sizes in Nano Transistors

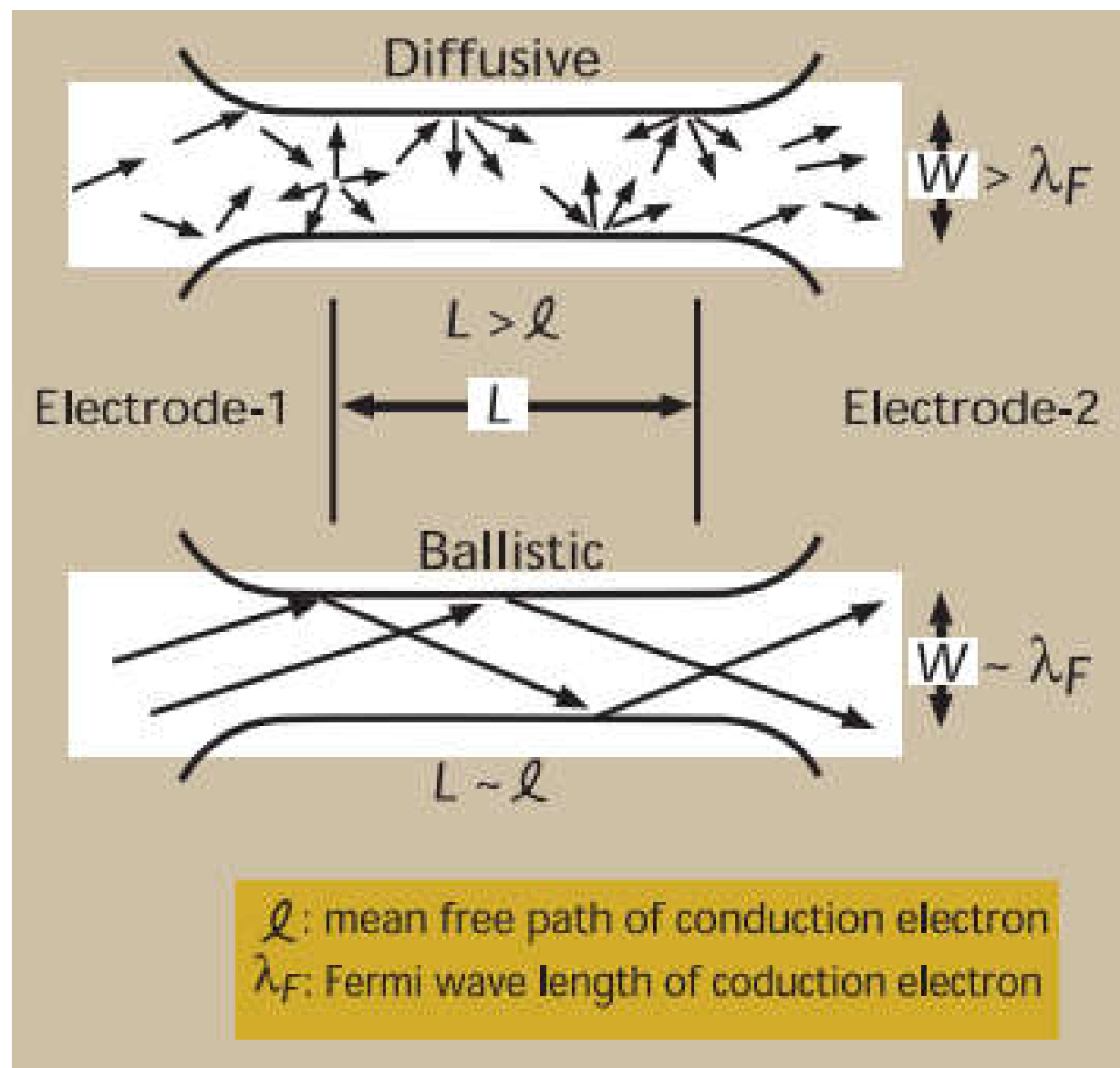


grain size ~ a few nm



*grain boundary, roughness,
increased electron scattering, ...*

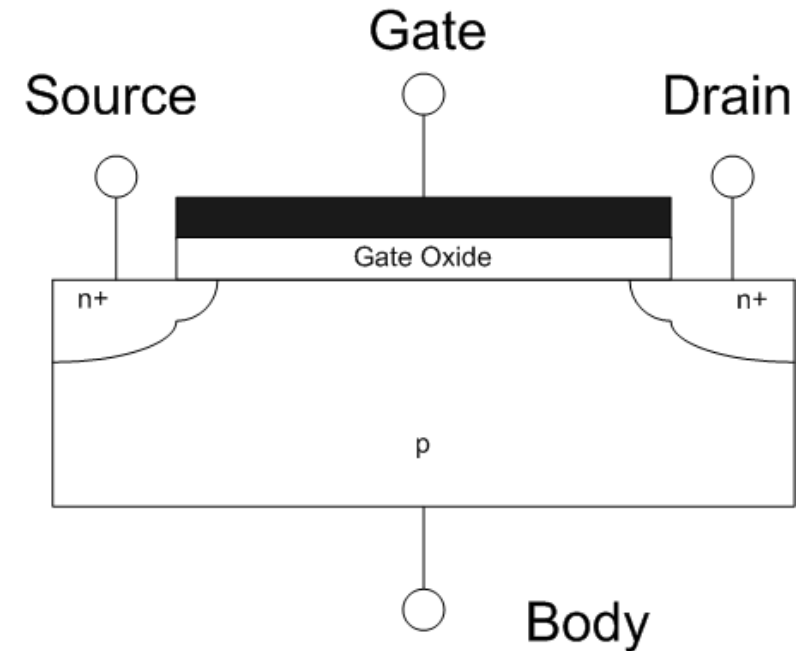
Carrier Transport



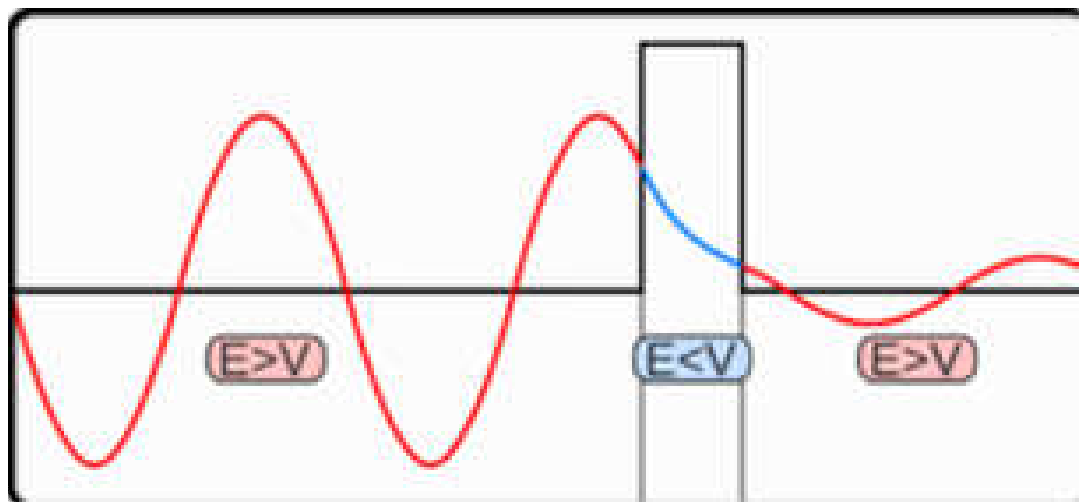
Carrier Transport

$$I_{D,Sat} = \frac{W}{L} \mu C \frac{(V_G - V_{th})^2}{2}$$

$$C = \frac{\kappa \epsilon_0 A}{t}$$

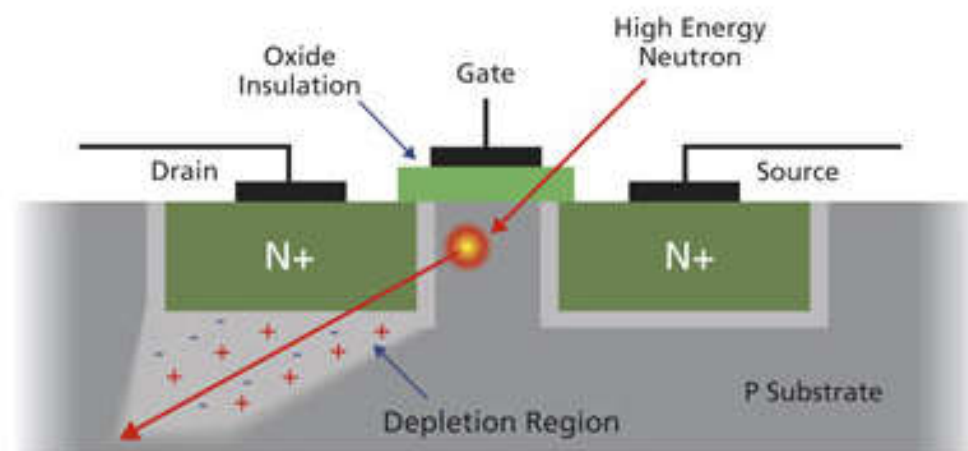
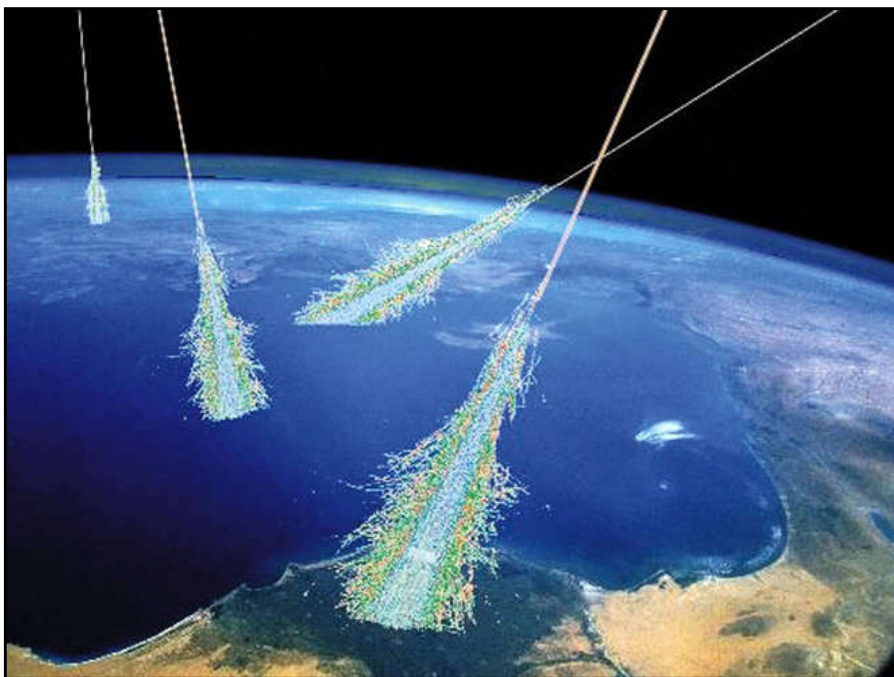


large C requires small t



quantum tunneling

Danger from Outer Space



smaller devices are more susceptible to cosmic rays

All Good Things Come to an End

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FEATURE NEWS

**THE SEMICONDUCTOR INDUSTRY
WILL SOON ABANDON ITS PURSUIT
OF MOORE'S LAW.
NOW THINGS COULD GET A LOT
MORE INTERESTING.**

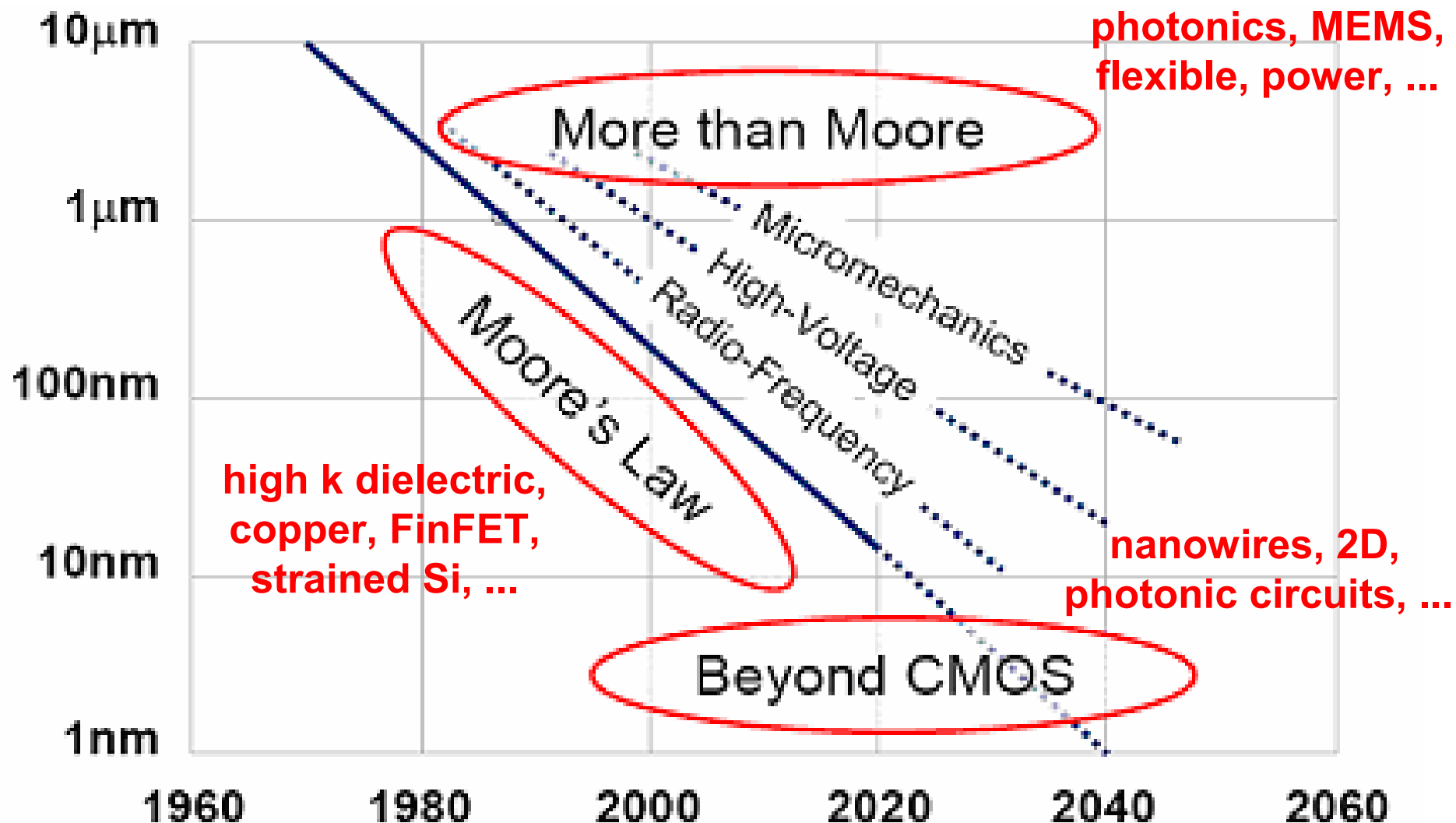
City. The Semiconductor Industry Association (SIA) in Washington DC, which represents all the major US firms, has already said that it will cease its participation in the road-mapping effort once the report is out, and will instead pursue its own research and development agenda.

Everyone agrees that the twilight of Moore's law will not mean the end of progress. "Think about what happened to airplanes," says Reed. "A Boeing 787 doesn't go any faster than a 707 did in the 1950s — but they are very different airplanes", with innovations ranging from fully electronic controls to a carbon-fibre fuselage. That's what will happen with computers, he says: "Innovation will absolutely continue — but it will be more nuanced and complicated."

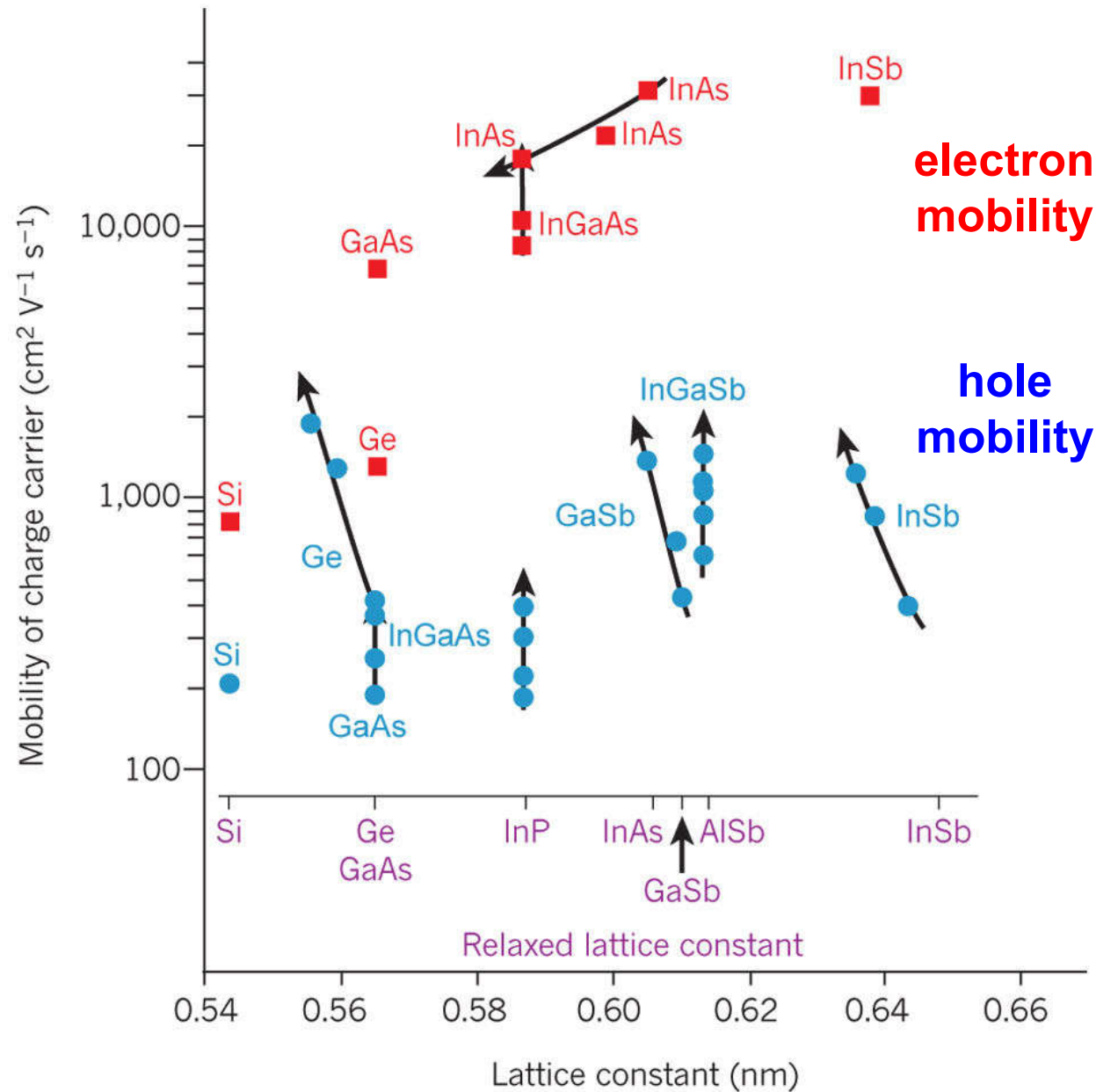
LAYING DOWN THE LAW
The 1965 essay¹ that would make Gordon Moore famous started with a meditation on what could be done with the still-new technology of integrated circuits. Moore, who was then research director of Fairchild

M. M. Waldrop, *Nature* **530**, 144 (2016)

New Opportunities



High Electron Mobility Transistor (HEMT)

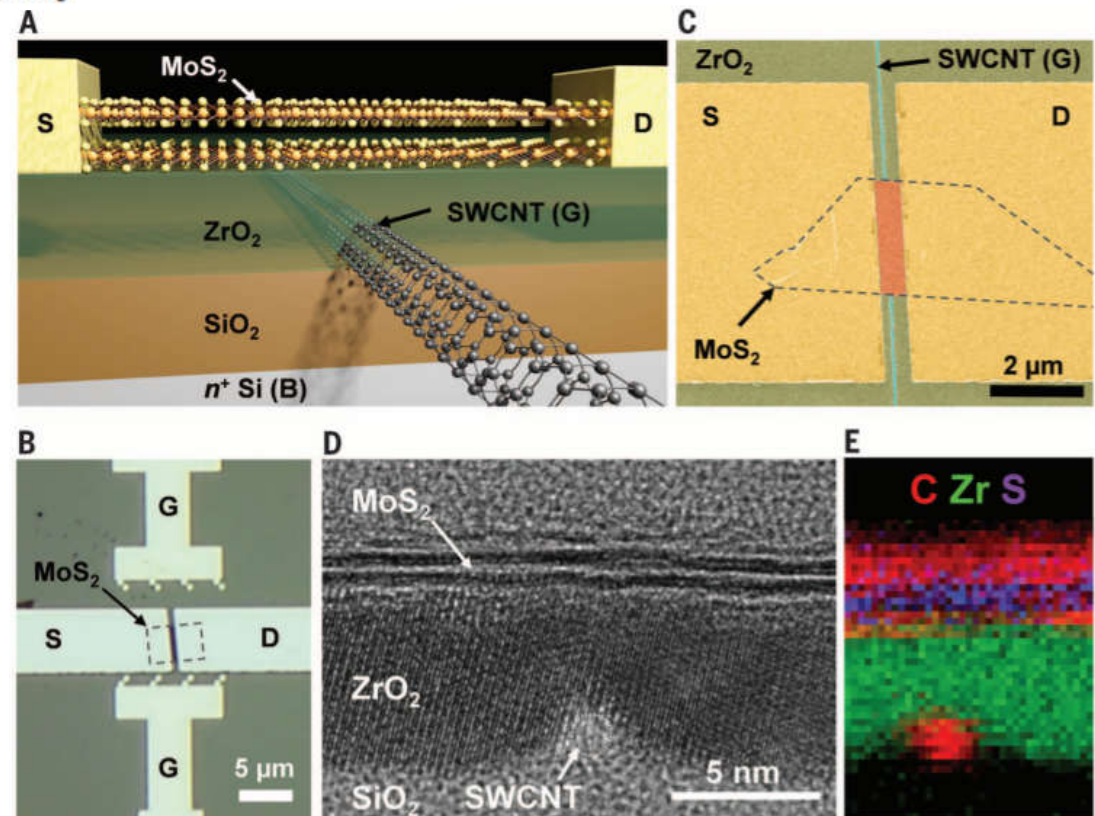


Nano-Transistors

DEVICE TECHNOLOGY

MoS₂ transistors with 1-nanometer gate lengths

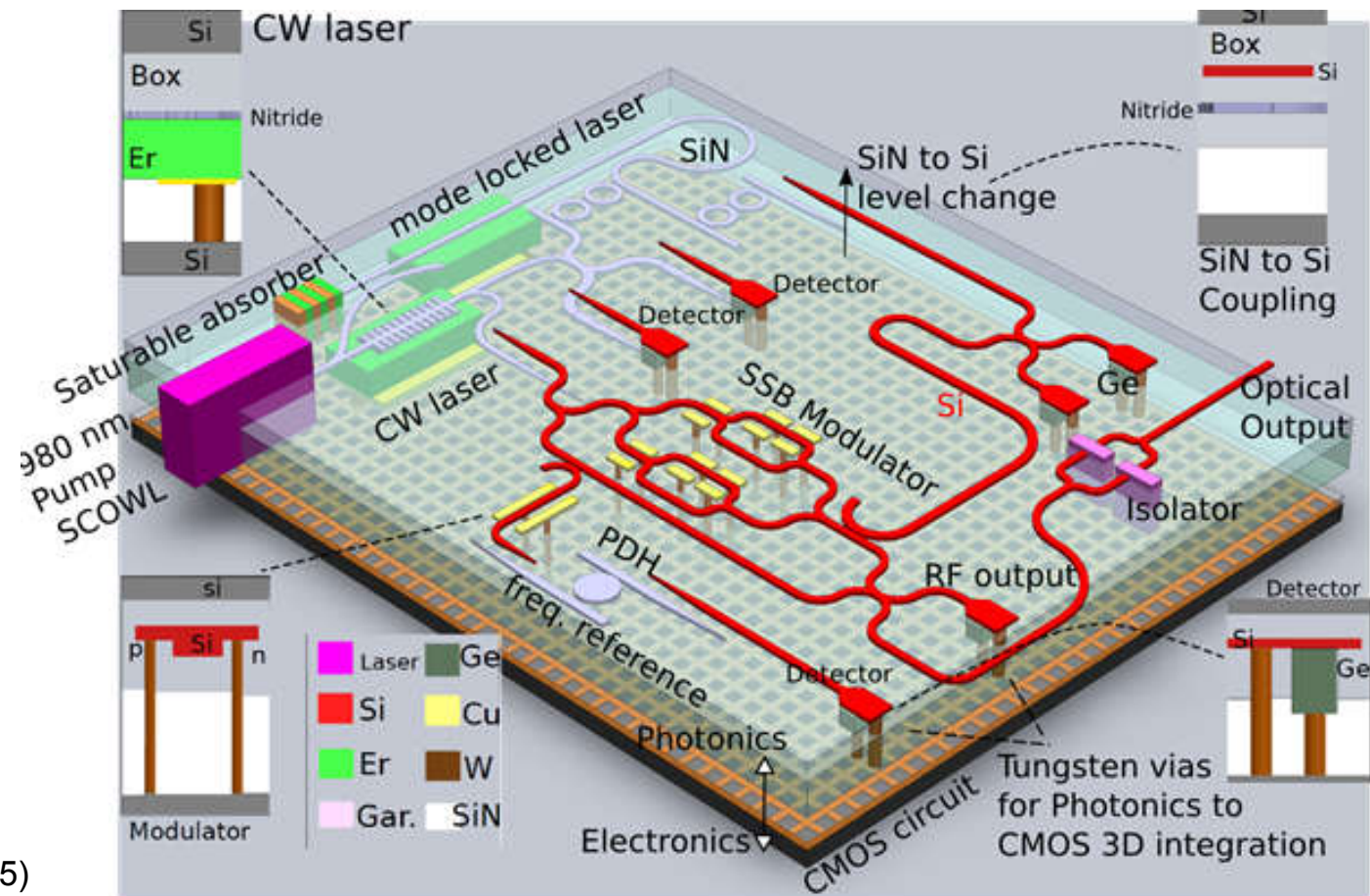
Sujay B. Desai,^{1,2,3} Surabhi R. Madhvapathy,^{1,2} Angada B. Sachid,^{1,2}
 Juan Pablo Llinas,^{1,2} Qingxiao Wang,⁴ Geun Ho Ahn,^{1,2} Gregory Pitner,⁵ Moon J. Kim,⁴
 Jeffrey Bokor,^{1,2} Chenming Hu,¹ H.-S. Philip Wong,⁵ Ali Javey^{1,2,3*}



Photonic Integrated Circuits

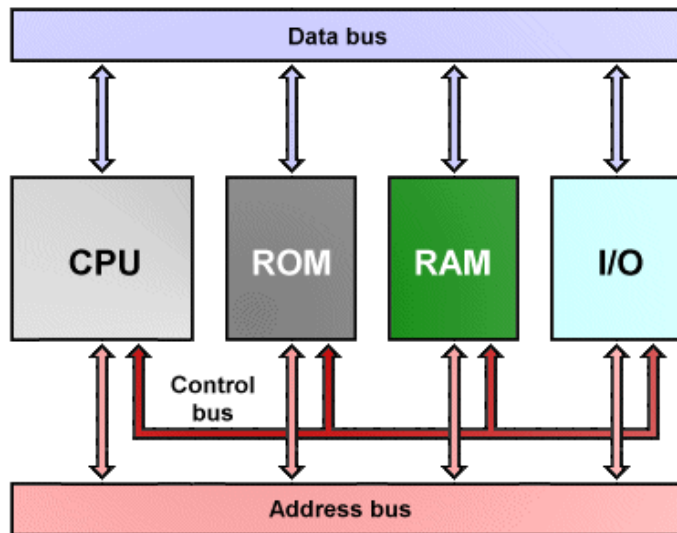
Single-chip microprocessor that communicates directly using light

Chen Sun^{1,2*}, Mark T. Wade^{3*}, Yunsup Lee^{1*}, Jason S. Orcutt^{2†*}, Luca Alloatti², Michael S. Georgas², Andrew S. Waterman¹, Jeffrey M. Shainline^{3†}, Rimas R. Avizienis¹, Sen Lin¹, Benjamin R. Moss², Rajesh Kumar³, Fabio Pavanello³, Amir H. Atabaki², Henry M. Cook¹, Albert J. Ou¹, Jonathan C. Leu², Yu-Hsin Chen², Krste Asanović¹, Rajeev J. Ram², Miloš A. Popović³ & Vladimir M. Stojanović¹

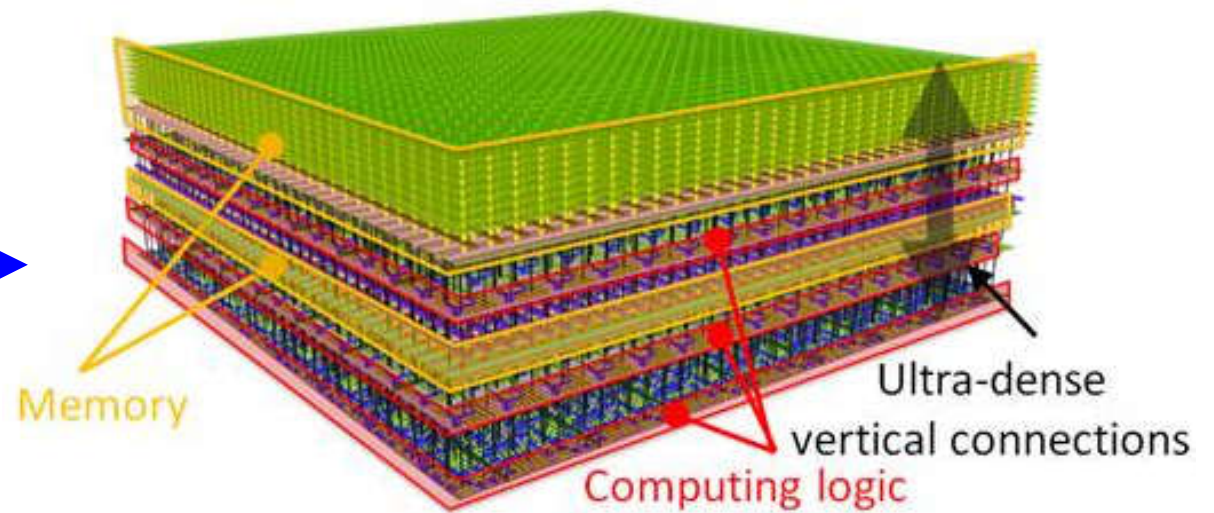


3D IC

- Logic + Memory + Sensing + ...

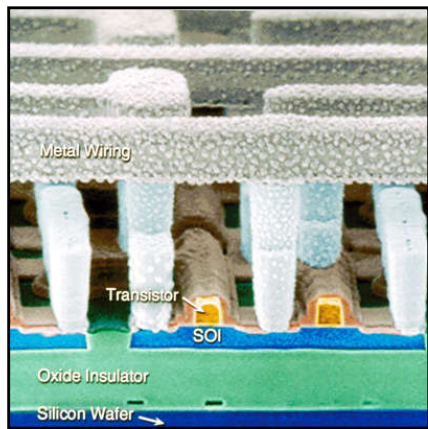


conventional

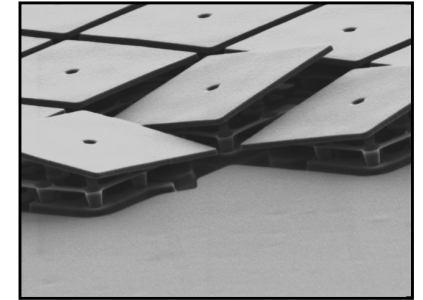
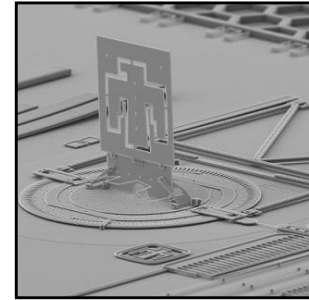
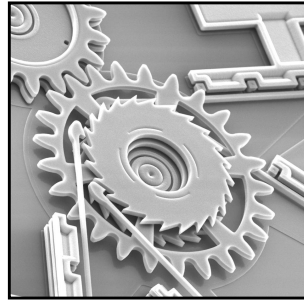


3D IC

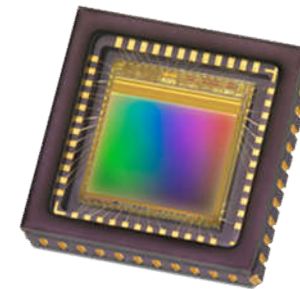
More than Moore



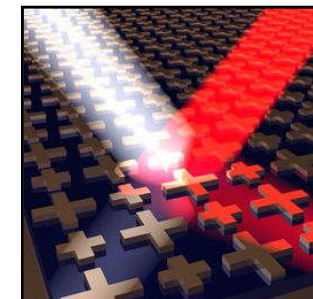
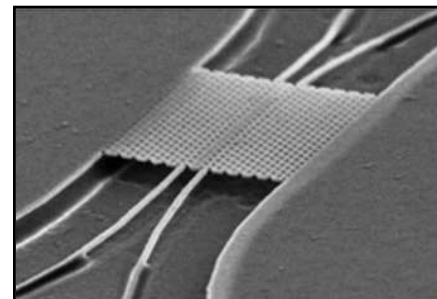
Microelectronics



Microelectromechanical Systems (MEMS)



Optoelectronics



Micro and Nano Photonics

Image Sensors



Anatomy of the Active Pixel Sensor Photodiode

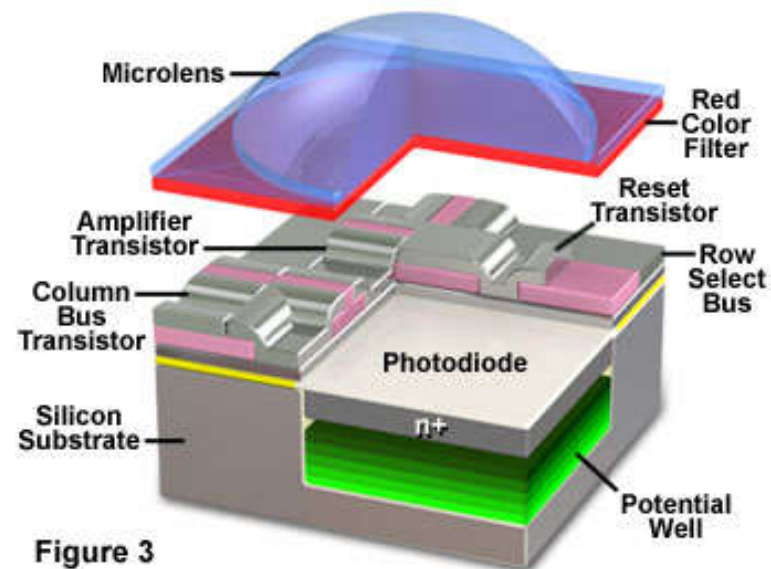
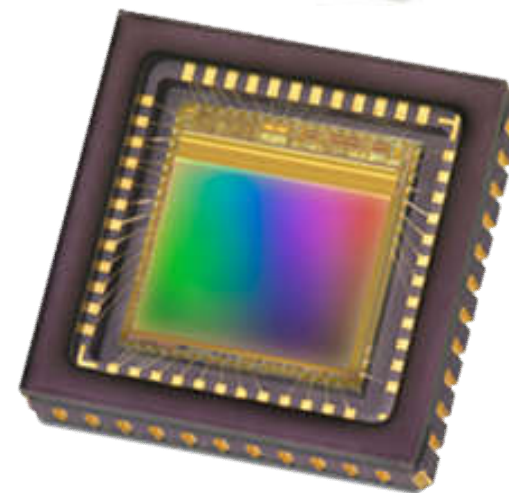


Figure 3

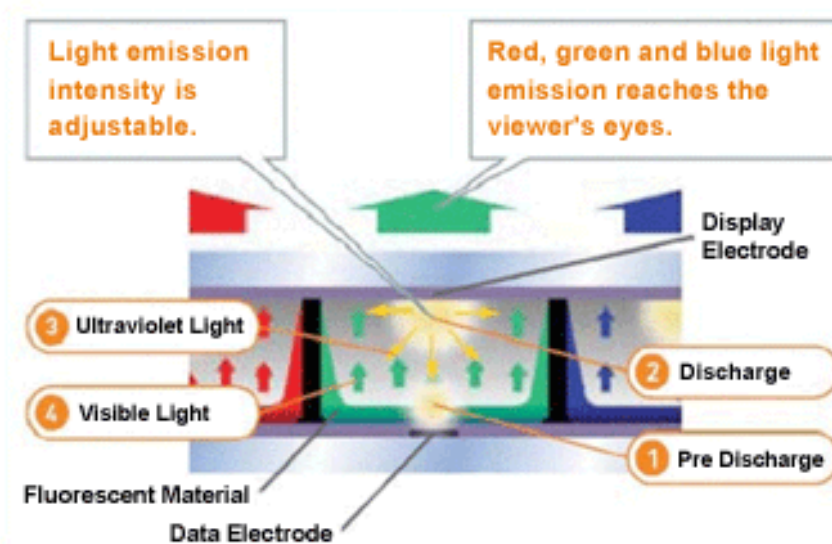
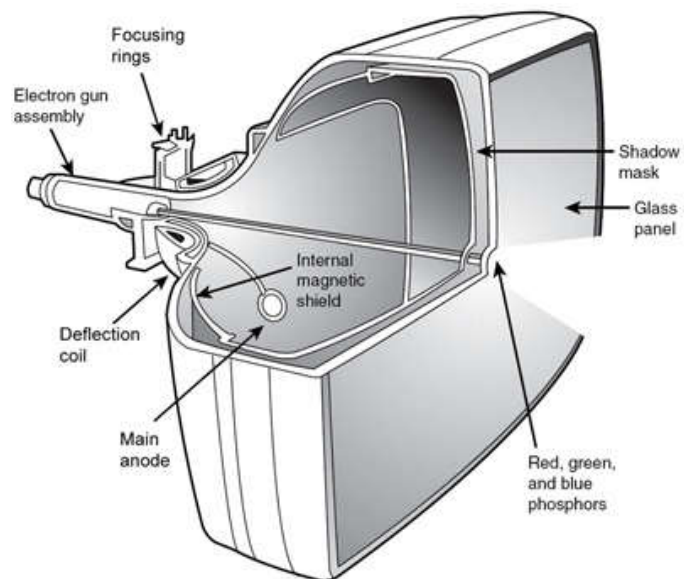


films

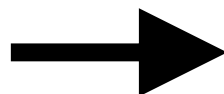


CMOS sensors

Displays



CRT

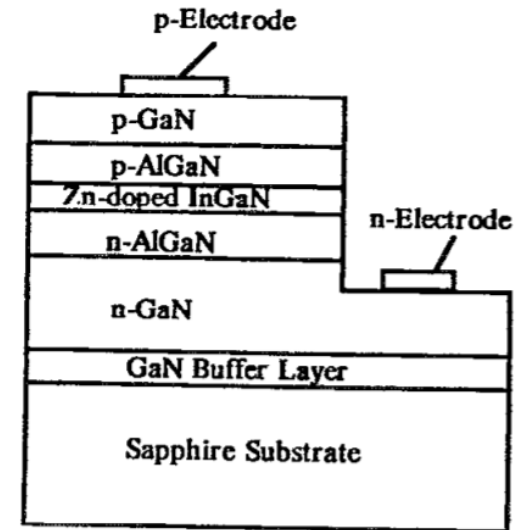
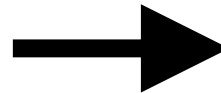


Flat panel

Light Sources



Incandescent bulb



S. Nakamura, *et al.*, *Appl. Phys. Lett.* **64**, 1687 (1994)

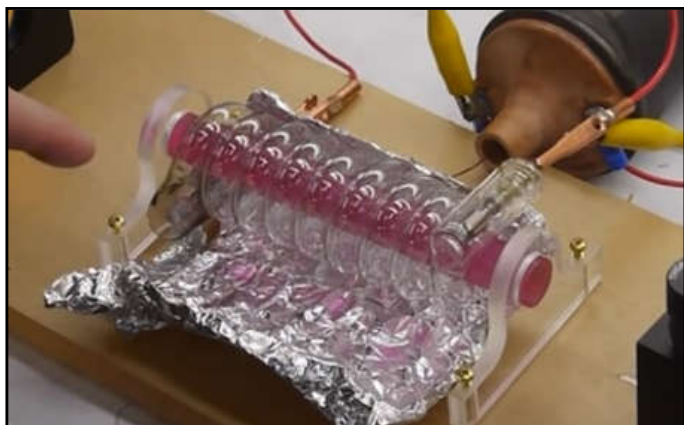


Fluorescent lamp



LEDs

Light Sources



ruby laser



gas laser

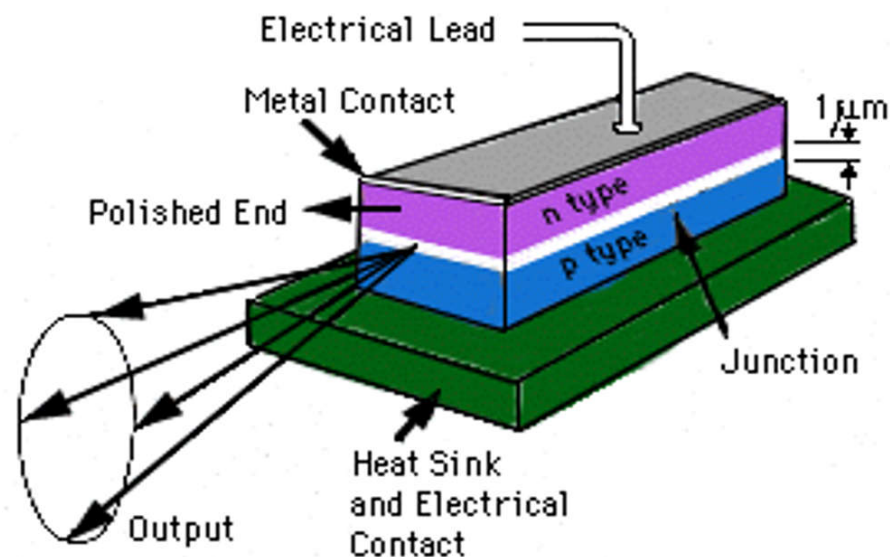


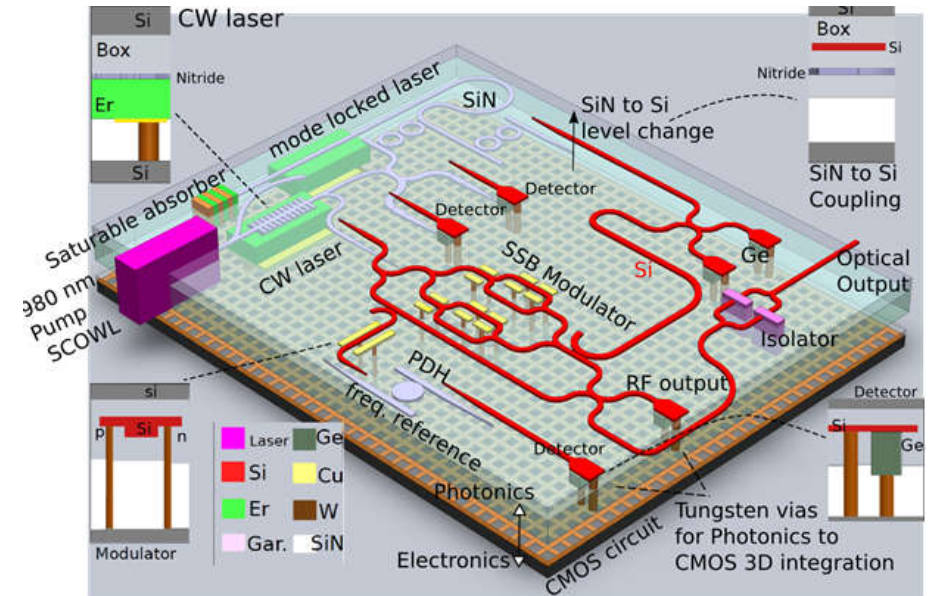
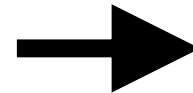
Diagram of Semiconductor Laser

semiconductor laser

Integrated Photonic Circuits



Conventional optics

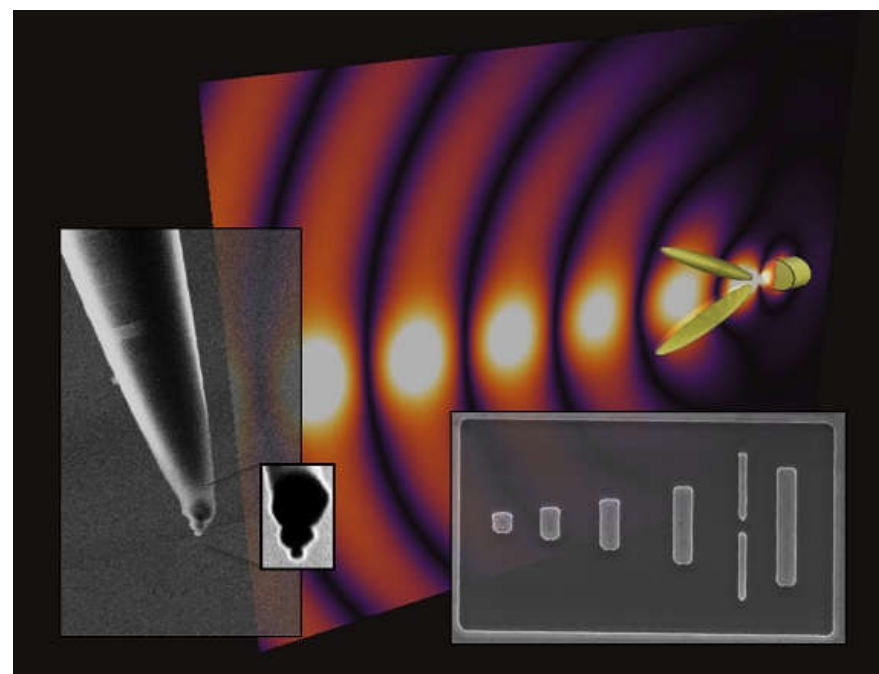


Integrated photonics

Integrated Photonic Circuits



Microwave Antenna



Optical Antenna